

HYS64T32x00HDL-[25F/2.5/3/3S/3.7/5]-B  
HYS64T64x20HDL-[25F/2.5/3/3S/3.7/5]-B  
HYS64T128x21HDL-[25F/2.5/3/3S/3.7/5]-B

*200 Pin Small-Outlined DDR2 SDRAMs Modules  
DDR2 SDRAM  
SO-DIMM SDRAM  
RoHS Compliant*

## Internet Data Sheet

*Rev. 1.12*

**HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module**

**HYS64T32x00HDL-[25F/2.5/3/3S/3.7/5]-B, HYS64T64x20HDL-[25F/2.5/3/3S/3.7/5]-B, HYS64T128x21HDL-[25F/2.5/3/3S/3.7/5]-B**

**Revision History: 2007-10, Rev. 1.12**

Page	Subjects (major changes since last revision)
6-11	Editorial changes and adapted to internet edition

**Previous Revision: 2006-10, Rev 1.11**

All	Editorial changes
-----	-------------------

**Previous Revision: 2006-10, Rev 1.10**

4	Added -25F Product Types; Added 6Layer -3S and -3.7 Product Types.
70, 71, 72	Updated Package Outline Drawings.

**Previous Revision: 2005-09, Rev 1.01**

All	Qimonda update
15	Modified AC Timing Parameters

**Previous Revision: 2005-06, Rev 1.0****We Listen to Your Comments**

Any information within this document that you feel is wrong, unclear or missing at all?

Your feedback will help us to continuously improve the quality of this document.

Please send your proposal (including a reference to this document) to:

[techdoc@qimonda.com](mailto:techdoc@qimonda.com)



# 1 Overview

This chapter gives an overview of the 200-pin Small-Outline DDR2 SDRAM modules product family and describes its main characteristics.

## 1.1 Features

- 200-Pin PC2-6400, PC2-5300, PC2-4200 and PC2-3200 DDR2 SDRAM memory modules.
- 32M × 64, 64M × 64 and 128M × 64 module organization, and 32M × 16, 64M × 8 chip organization
- 256MB, 512MB and 1GB modules built with 512-Mbit DDR2 SDRAMs in P-TFBGA-84 and P-TFBGA-60 chipsize packages
- Standard Double-Data-Rate-Two Synchronous DRAMs (DDR2 SDRAM) with a single + 1.8 V ( $\pm 0.1$  V) power supply
- All speed grades faster than DDR2-400 comply with DDR2-400 timing specifications.
- Programmable CAS Latencies (3, 4, 5 and 6), Burst Length (8 & 4).
- Auto Refresh (CBR) and Self Refresh
- Auto Refresh for temperatures above 85 °C  $t_{REFI} = 3.9$  µs.
- Programmable self refresh rate via EMRS2 setting.
- Programmable partial array refresh via EMRS2 settings.
- DCC enabling via EMRS2 setting.
- All inputs and outputs SSTL\_1.8 compatible
- Off-Chip Driver Impedance Adjustment (OCD) and On-Die Termination (ODT)
- Serial Presence Detect with E<sup>2</sup>PROM
- SO-DIMM Dimensions (nominal): 30 mm high, 67.6 mm wide
- Based on standard reference layouts Raw Cards 'A', 'C', and 'E'
- RoHS compliant products<sup>1)</sup>

**TABLE 1**  
Performance Table

QAG Speed Code		-25F	-2.5	-3	-3S	-3.7	-5	Unit
DRAM Speed Grade		DDR2	-800D	-800E	-667C	-667D	-533C	
Module Speed Grade		PC2	-6400D	-6400E	-5300C	-5300D	-4200C	-3200B
CAS-RCD-RP latencies		5-5-5	6-6-6	4-4-4	5-5-5	4-4-4	3-3-3	$t_{CK}$
Max. Clock Frequency	CL3	$f_{CK3}$	200	200	200	200	200	MHz
	CL4	$f_{CK4}$	266	266	333	266	266	MHz
	CL5	$f_{CK5}$	400	333	333	333	266	– MHz
	CL6	$f_{CK6}$	–	400	–	–	–	MHz
Min. RAS-CAS-Delay		$t_{RCD}$	12.5	15	12	15	15	ns
Min. Row Precharge Time		$t_{RP}$	12.5	15	12	15	15	ns
Min. Row Active Time		$t_{RAS}$	45	45	45	45	40	ns
Min. Row Cycle Time		$t_{RC}$	57.5	60	57	60	60	55 ns

1) RoHS Compliant Product: Restriction of the use of certain hazardous substances (RoHS) in electrical and electronic equipment as defined in the directive 2002/95/EC issued by the European Parliament and of the Council of 27 January 2003. These substances include mercury, lead, cadmium, hexavalent chromium, polybrominated biphenyls and polybrominated biphenyl ethers.

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

## 1.2 Description

The Qimonda HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B module family are small-outline DIMM modules "SO-DIMMs" with 30 mm height based on DDR2 technology. DIMMs are available as non-ECC modules in 128M × 64 (1GB), 32M × 64 (256MB), 64M × 64 (512MB) in organization and density, intended for mounting into 200-pin connector sockets.

The memory array is designed with 512MBit Double-Data-Rate-Two (DDR2) Synchronous DRAMs. Decoupling capacitors are mounted on the PCB board. The DIMMs feature serial presence detect based on a serial E<sup>2</sup>PROM device using the 2-pin I<sup>2</sup>C protocol. The first 128 bytes are programmed with configuration data and are write protected; the second 128 bytes are available to the customer.



**TABLE 2**  
**Ordering Information for RoHS Compliant Products**

Product Type <sup>1)</sup>	Compliance Code <sup>2)</sup>	Description	SDRAM Technology
<b>PC2-6400-555</b>			
HYS64T32000HDL-25F-B	256MB 1R×16 PC2-6400S-555-12-C0	1 Rank, Non-ECC	512Mbit (×16)
HYS64T64020HDL-25F-B	512MB 2R×16 PC2-6400S-555-12-A0	2 Ranks, Non-ECC	512Mbit (×16)
HYS64T128021HDL-25F-B	1GB 2R×8 PC2-6400S-555-12-E0	2 Ranks, Non-ECC	512Mbit (×8)
<b>PC2-6400-666</b>			
HYS64T32000HDL-2.5-B	256MB 1R×16 PC2-6400S-666-12-C0	1 Rank, Non-ECC	512Mbit (×16)
HYS64T64020HDL-2.5-B	512MB 2R×16 PC2-6400S-666-12-A0	2 Ranks, Non-ECC	512Mbit (×16)
HYS64T128021HDL-2.5-B	1GB 2R×8 PC2-6400S-666-12-E0	2 Ranks, Non-ECC	512Mbit (×8)
<b>PC2-5300-444</b>			
HYS64T32000HDL-3-B	256MB 1R×16 PC2-5300S-444-12-C0	1 Rank, Non-ECC	512Mbit (×16)
HYS64T64020HDL-3-B	512MB 2R×16 PC2-5300S-444-12-A0	2 Ranks, Non-ECC	512Mbit (×16)
HYS64T128021HDL-3-B	1GB 2R×8 PC2-5300S-444-12-E0	2 Ranks, Non-ECC	512Mbit (×8)
<b>PC2-5300-555</b>			
HYS64T32000HDL-3S-B	256MB 1R×16 PC2-5300S-555-12-C0	1 Rank, Non-ECC	512Mbit (×16)
HYS64T32900HDL-3S-B	256MB 1R×16 PC2-5300S-555-12-C0	1 Rank, Non-ECC	512Mbit (×16)
HYS64T64020HDL-3S-B	512MB 2R×16 PC2-5300S-555-12-A0	2 Ranks, Non-ECC	512Mbit (×16)
HYS64T64920HDL-3S-B	512MB 2R×16 PC2-5300S-555-12-A0	2 Ranks, Non-ECC	512Mbit (×16)
HYS64T128021HDL-3S-B	1GB 2R×8 PC2-5300S-555-12-E0	2 Ranks, Non-ECC	512Mbit (×8)
HYS64T128921HDL-3S-B	1GB 2R×8 PC2-5300S-555-12-E0	2 Ranks, Non-ECC	512Mbit (×8)
<b>PC2-4200-444</b>			
HYS64T32000HDL-3.7-B	256MB 1R×16 PC2-4200S-444-12-C0	1 Rank, Non-ECC	512Mbit (×16)
HYS64T32900HDL-3.7-B	256MB 1R×16 PC2-4200S-444-12-C0	1 Rank, Non-ECC	512Mbit (×16)
HYS64T64020HDL-3.7-B	512MB 2R×16 PC2-4200S-444-12-A0	2 Ranks, Non-ECC	512Mbit (×16)
HYS64T64920HDL-3.7-B	512MB 2R×16 PC2-4200S-444-12-A0	2 Ranks, Non-ECC	512Mbit (×16)
HYS64T128021HDL-3.7-B	1GB 2R×8 PC2-4200S-444-12-E0	2 Ranks, Non-ECC	512Mbit (×8)
HYS64T128921HDL-3.7-B	1GB 2R×8 PC2-4200S-444-12-E0	2 Ranks, Non-ECC	512Mbit (×8)
<b>PC2-3200-333</b>			
HYS64T32000HDL-5-B	256MB 1R×16 PC2-3200S-333-12-C0	1 Rank, Non-ECC	512Mbit (×16)



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type <sup>1)</sup>	Compliance Code <sup>2)</sup>	Description	SDRAM Technology
HYS64T64020HDL-5-B	512MB 2Rx16 PC2-3200S-333-12-A0	2 Ranks, Non-ECC	512Mbit (x16)
HYS64T128021HDL-5-B	1GB 2Rx8 PC2-3200S-333-12-E0	2 Ranks, Non-ECC	512Mbit (x8)

- 1) For detailed information regarding Product Type of Qimonda please see chapter "Product Type Nomenclature" of this datasheet.  
 2) The Compliance Code is printed on the module label and describes the speed grade, for example "PC2-6400S-555-12-E0" where 6400S means Small-Outline DIMM modules with 6.40 GB/sec Module Bandwidth and "555-12" means Column Address Strobe (CAS) latency =5, Row Column Delay (RCD) latency = 5 and Row Precharge (RP) latency = 5 using the latest JEDEC SPD Revision 1.2 and produced on the Raw Card "E".

**TABLE 3**  
**Address Format**

DIMM Density	Module Organization	Memory Ranks	ECC/ Non-ECC	# of SDRAMs	# of row/bank/column bits	Raw Card
1GB	128M x 64	2	Non-ECC	16	14/2/10	E
512MB	64M x 64	2	Non-ECC	8	13/2/10	A
256MB	32M x 64	1	Non-ECC	4	13/2/10	C

**TABLE 4**  
**Components on Modules**

Product Type <sup>1)2)</sup>	DRAM Components <sup>1)</sup>	DRAM Density	DRAM Organisation
HYS64T128021HDL	HYB18T512800BF	512Mbit	64M x 8
HYS64T128921HDL			
HYS64T64020HDL	HYB18T512160BF	512Mbit	32M x 16
HYS64T64920HDL			
HYS64T32000HDL	HYB18T512160BF	512Mbit	32M x 16
HYS64T32900HDL			

- 1) Green Product  
 2) For a detailed description of all functionalities of the DRAM components on these modules see the component data sheet.

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

## 2 Pin Configurations

### 2.1 Pin Configurations

The pin configuration of the Small Outline DDR2 SDRAM DIMM is listed by function in **Table 5** (200 pins). The abbreviations used in columns Pin Type and Buffer Type are explained in **Table 6** and **Table 7** respectively. The Pin numbering is depicted in **Figure 1**

**TABLE 5**  
Pin Configuration of SO-DIMM

Pin No.	Name	Pin Type	Buffer Type	Function
<b>Clock Signals</b>				
30	CK0	I	SSTL	<b>Clock Signals 1:0, Complement Clock Signals 1:0</b> The system clock inputs. All address and command lines are sampled on the cross point of the rising edge of CK and the falling edge of CK. A Delay Locked Loop (DLL) circuit is driven from the clock inputs and output timing for read operations is synchronized to the input clock.
164	CK1	I	SSTL	
32	CK0	I	SSTL	
166	CK1	I	SSTL	
79	CKE0	I	SSTL	<b>Clock Enable Rank 1:0</b> Activates the DDR2 SDRAM CK signal when HIGH and deactivates the CK signal when LOW. By deactivating the clocks, CKE LOW initiates the Power Down Mode or the Self Refresh Mode. <i>Note: 2 Ranks module</i>
80	CKE1	I	SSTL	
	NC	NC	—	<b>Not Connected</b> <i>Note: 1-rank module</i>
<b>Control Signals</b>				
110	S0	I	SSTL	<b>Chip Select Rank 1:0</b>
115	S1	I	SSTL	Enables the associated DDR2 SDRAM command decoder when LOW and disables the command decoder when HIGH. When the command decoder is disabled, new commands are ignored but previous operations continue. Rank 0 is selected by S0; Rank 1 is selected by S1. Ranks are also called "Physical banks". <i>2 Ranks module</i>
	NC	NC	—	<b>Not Connected</b> <i>Note: 1-rank module</i>
108	RAS	I	SSTL	<b>Row Address Strobe</b> When sampled at the cross point of the rising edge of CK, and falling edge of CK, RAS, CAS and WE define the operation to be executed by the SDRAM.
113	CAS	I	SSTL	<b>Column Address Strobe</b>

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Pin No.	Name	Pin Type	Buffer Type	Function
109	WE	I	SSTL	<b>Write Enable</b>
<b>Address Signals</b>				
107	BA0	I	SSTL	<b>Bank Address Bus 2:0</b>
106	BA1	I	SSTL	Selects which DDR2 SDRAM internal bank of four or eight is activated.
85	BA2	I	SSTL	<b>Bank Address Bus 2</b> Greater than 512Mb DDR2 SDRAMs
	NC	NC	SSTL	<b>Less than 1Gb DDR2 SDRAMs</b>
102	A0	I	SSTL	<b>Address Bus 12:0</b>
101	A1	I	SSTL	During a Bank Activate command cycle, defines the row address when sampled at the cross-point of the rising edge of CK and falling edge of $\overline{CK}$ . During a Read or Write command cycle, defines the column address when sampled at the cross point of the rising edge of CK and falling edge of $\overline{CK}$ . In addition to the column address, AP is used to invoke autoprecharge operation at the end of the burst read or write cycle. If AP is HIGH, autoprecharge is selected and BA0-BAn defines the bank to be precharged. If AP is LOW, autoprecharge is disabled. During a Precharge command cycle, AP is used in conjunction with BA0-BAn to control which bank(s) to precharge. If AP is HIGH, all banks will be precharged regardless of the state of BA0-BAn inputs. If AP is LOW, then BA0-BAn are used to define which bank to precharge.
100	A2	I	SSTL	
99	A3	I	SSTL	
98	A4	I	SSTL	
97	A5	I	SSTL	
94	A6	I	SSTL	
92	A7	I	SSTL	
93	A8	I	SSTL	
91	A9	I	SSTL	
105	A10	I	SSTL	
	AP	I	SSTL	
90	A11	I	SSTL	
89	A12	I	SSTL	<b>Address Signal 12</b> <i>Note: Module based on 256 Mbit or larger dies</i>
116	A13	I	SSTL	<b>Address Signal 13</b> <i>Note: 1 Gbit based module</i>
	NC	NC	—	<b>Not Connected</b> <i>Note: Module based on 512 Mbit or smaller dies</i>
86	A14	I	SSTL	<b>Address Signal 14</b> <i>Note: 2 Gbit based module</i>
	NC	NC	—	<b>Not Connected</b> <i>Note: Module based on 1 Gbit or smaller dies</i>
<b>Data Signals</b>				

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Pin No.	Name	Pin Type	Buffer Type	Function
5	DQ0	I/O	SSTL	<b>Data Bus 63:0</b> <i>Note: Data Input / Output pins</i>
7	DQ1	I/O	SSTL	
17	DQ2	I/O	SSTL	
19	DQ3	I/O	SSTL	
4	DQ4	I/O	SSTL	
6	DQ5	I/O	SSTL	
14	DQ6	I/O	SSTL	
16	DQ7	I/O	SSTL	
23	DQ8	I/O	SSTL	
25	DQ9	I/O	SSTL	
35	DQ10	I/O	SSTL	
37	DQ11	I/O	SSTL	
20	DQ12	I/O	SSTL	
22	DQ13	I/O	SSTL	
36	DQ14	I/O	SSTL	
38	DQ15	I/O	SSTL	
43	DQ16	I/O	SSTL	
45	DQ17	I/O	SSTL	
55	DQ18	I/O	SSTL	
57	DQ19	I/O	SSTL	
44	DQ20	I/O	SSTL	
46	DQ21	I/O	SSTL	
56	DQ22	I/O	SSTL	
58	DQ23	I/O	SSTL	
61	DQ24	I/O	SSTL	
63	DQ25	I/O	SSTL	
73	DQ26	I/O	SSTL	
75	DQ27	I/O	SSTL	
62	DQ28	I/O	SSTL	
64	DQ29	I/O	SSTL	
74	DQ30	I/O	SSTL	
76	DQ31	I/O	SSTL	
123	DQ32	I/O	SSTL	
125	DQ33	I/O	SSTL	
135	DQ34	I/O	SSTL	
137	DQ35	I/O	SSTL	
124	DQ36	I/O	SSTL	
126	DQ37	I/O	SSTL	
134	DQ38	I/O	SSTL	
136	DQ39	I/O	SSTL	

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Pin No.	Name	Pin Type	Buffer Type	Function
141	DQ40	I/O	SSTL	<b>Data Bus 63:0</b> <i>Note: Data Input / Output pins</i>
143	DQ41	I/O	SSTL	
151	DQ42	I/O	SSTL	
153	DQ43	I/O	SSTL	
140	DQ44	I/O	SSTL	
142	DQ45	I/O	SSTL	
152	DQ46	I/O	SSTL	
154	DQ47	I/O	SSTL	
157	DQ48	I/O	SSTL	
159	DQ49	I/O	SSTL	
173	DQ50	I/O	SSTL	
175	DQ51	I/O	SSTL	
158	DQ52	I/O	SSTL	
160	DQ53	I/O	SSTL	
174	DQ54	I/O	SSTL	
176	DQ55	I/O	SSTL	
179	DQ56	I/O	SSTL	
181	DQ57	I/O	SSTL	
189	DQ58	I/O	SSTL	
191	DQ59	I/O	SSTL	
180	DQ60	I/O	SSTL	
182	DQ61	I/O	SSTL	
192	DQ62	I/O	SSTL	
194	DQ63	I/O	SSTL	

**Data Strobe Signals**

13	DQS0	I/O	SSTL	<b>Data Strobe Bus 7:0</b> The data strobes, associated with one data byte, sourced with data transfers. In Write mode, the data strobe is sourced by the controller and is centered in the data window. In Read mode the data strobe is sourced by the DDR2 SDRAM and is sent at the leading edge of the data window. DQS signals are complements, and timing is relative to the cross-point of respective DQS and $\overline{DQS}$ . If the module is to be operated in single ended strobe mode, all $\overline{DQS}$ signals must be tied on the system board to $V_{SS}$ and DDR2 SDRAM mode registers programmed appropriately.
11	$\overline{DQS0}$	I/O	SSTL	
31	DQS1	I/O	SSTL	
29	$\overline{DQS1}$	I/O	SSTL	
51	DQS2	I/O	SSTL	
49	$\overline{DQS2}$	I/O	SSTL	
70	DQS3	I/O	SSTL	
68	$\overline{DQS3}$	I/O	SSTL	
131	DQS4	I/O	SSTL	
129	$\overline{DQS4}$	I/O	SSTL	
148	DQS5	I/O	SSTL	
146	$\overline{DQS5}$	I/O	SSTL	
169	DQS6	I/O	SSTL	
167	$\overline{DQS6}$	I/O	SSTL	
188	DQS7	I/O	SSTL	

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Pin No.	Name	Pin Type	Buffer Type	Function
186	DQS7	I/O	SSTL	<b>Data Strobe Bus 7:0</b>
<b>Data Mask Signals</b>				
10	DM0	I	SSTL	<b>Data Mask Bus 7:0</b>
26	DM1	I	SSTL	The data write masks, associated with one data byte. In Write mode, DM operates as a byte mask by allowing input data to be written if it is LOW but blocks the write operation if it is HIGH. In Read mode, DM lines have no effect.
52	DM2	I	SSTL	
67	DM3	I	SSTL	
130	DM4	I	SSTL	
147	DM5	I	SSTL	
170	DM6	I	SSTL	
185	DM7	I	SSTL	
<b>EEPROM</b>				
197	SCL	I	CMOS	<b>Serial Bus Clock</b> This signal is used to clock data into and out of the SPD EEPROM and Thermal sensor.
195	SDA	I/O	OD	<b>Serial Bus Data</b> This is a bidirectional pin use to transfer data into and out of the SPD EEPROM and Thermal sensor. A resistor must be connected from SDA to $V_{DDSPD}$ on the motherboard to act as a pull-up.
198	SA0	I	CMOS	<b>Serial Address Select Bus 2:0</b>
200	SA1	I	CMOS	Address pins used to select the SPD and Thermal sensor base address.
50	EVENT	O	OD	<b>EVENT</b> The optional EVENT pin is reserved for use to flag critical module temperature and is used in conjunction with Thermal Sensor.
	NC	-	-	<b>Not Connected</b> Not connected on modules without temperature sensors.
<b>Power Supplies</b>				
1	$V_{REF}$	AI	—	<b>I/O Reference Voltage</b> Reference voltage for the SSTL-18 inputs.
199	$V_{DDSPD}$	PWR	—	<b>EEPROM Power Supply</b> Power supplies for Serial Presence Detect, Thermal Sensor and ground for the module.
81,82,87,88,95,96,103,104, 111,112,117,118	$V_{DD}$	PWR	—	<b>Power Supply</b> Power supplies for core, I/O and ground for the module.
2,3,8,9,12,15,18,21,24,27,28, 33,34,39,40,41,42,47,48,53, 54,59,60,65,66,71,72,77,78, 121,122,127,128,132,133,138,13 9,144,145,149,150,155,156, 161,162,165,168, 171,172,177, 178,183,184,187,190,193,196	$V_{SS}$	GND	—	<b>Ground Plane</b> Power supplies for core, I/O, Serial Presence Detect, Thermal Sensor and ground for the module.
<b>Other pins</b>				
114	ODT0	I	SSTL	<b>On-Die Termination Control 1:0</b>

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

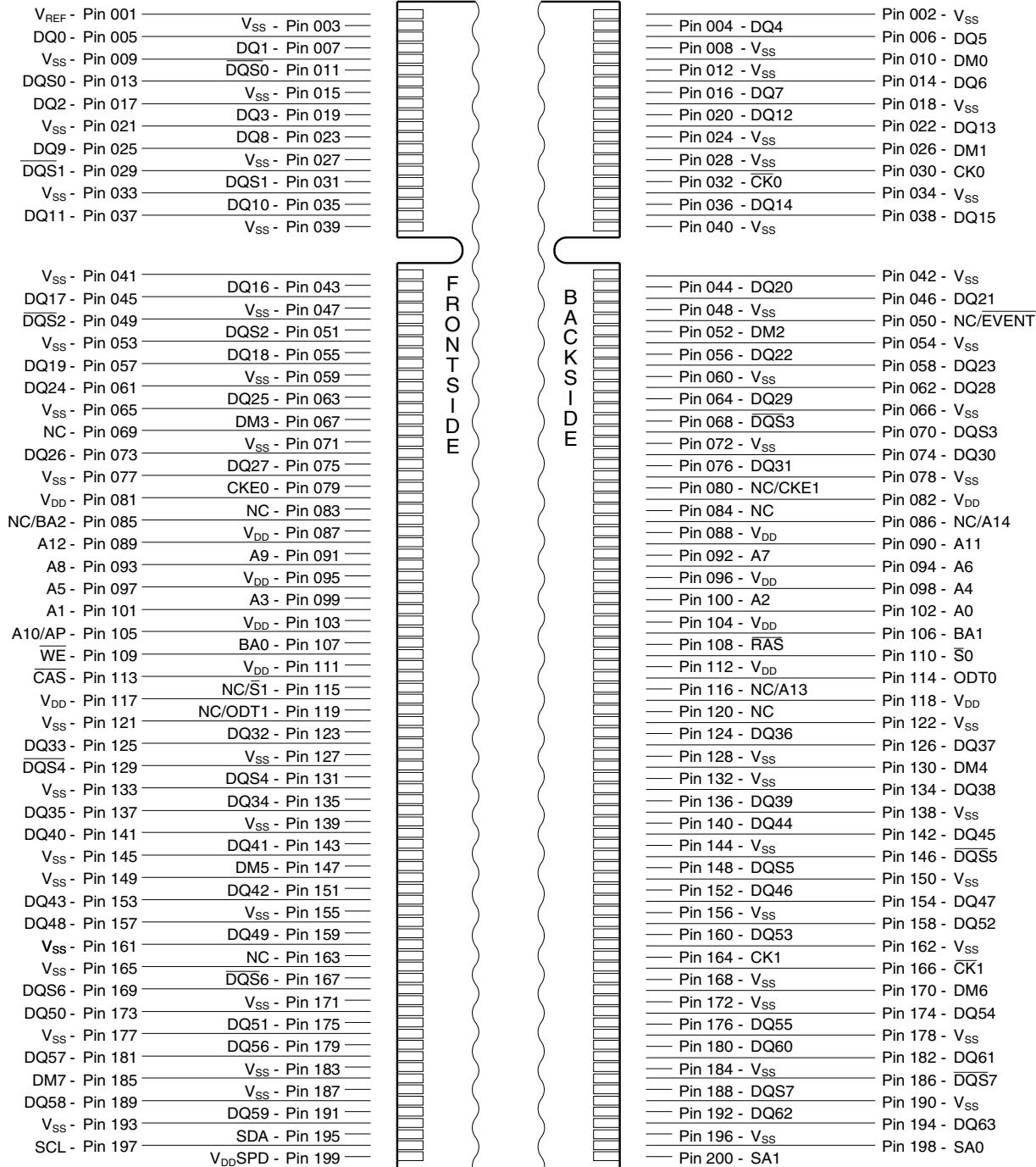
Pin No.	Name	Pin Type	Buffer Type	Function
119	ODT1	I	SSTL	<b>On-Die Termination Control 1</b> Asserts on-die termination for DQ, DM, DQS, and $\overline{DQS}$ signals if enabled via the DDR2 SDRAM mode register. <i>Note: 2 Rank modules</i>
	NC	NC	—	<b>Not Connected</b> <i>Note: 1 Rank modules</i>
69,83,84,120,163	NC	NC	—	<b>Not connected</b> Pins not connected on Qimonda SO-DIMMs

**TABLE 6**  
Abbreviations for pin Type

Abbreviation	Description
I	Standard input-only pin. Digital levels.
O	Output. Digital levels.
I/O	I/O is a bidirectional input/output signal.
AI	Input. Analog levels.
PWR	Power
GND	Ground
NC	Not Connected

**TABLE 7**  
Abbreviations for Buffer Type

Abbreviation	Description
SSTL	Serial Stub Terminated Logic (SSTL_18)
LV-CMOS	Low Voltage CMOS
CMOS	CMOS Levels
OD	Open Drain. The corresponding pin has 2 operational states, active low and tri-state, and allows multiple devices to share as a wire-OR.

**HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module****FIGURE 1**  
**Pin Configuration SO-DIMM (200 pin)**

MPPT0140

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

## 3 Electrical Characteristics

### 3.1 Absolute Maximum Ratings

**Attention: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.**

**TABLE 8**  
**Absolute Maximum Ratings**

Symbol	Parameter	Rating		Unit	Note
		Min.	Max.		
$V_{DD}$	Voltage on $V_{DD}$ pin relative to $V_{SS}$	-1.0	+2.3	V	<sup>1)</sup>
$V_{DDQ}$	Voltage on $V_{DDQ}$ pin relative to $V_{SS}$	-0.5	+2.3	V	<sup>1)</sup> <sup>1)</sup>
$V_{DDL}$	Voltage on $V_{DDL}$ pin relative to $V_{SS}$	-0.5	+2.3	V	<sup>1)</sup> <sup>1)</sup>
$V_{IN}, V_{OUT}$	Voltage on any pin relative to $V_{SS}$	-0.5	+2.3	V	<sup>1)</sup>

1) When  $V_{DD}$  and  $V_{DDQ}$  and  $V_{DDL}$  are less than 500 mV;  $V_{REF}$  may be equal to or less than 300 mV.

**TABLE 9**  
**Environmental Requirements**

Parameter	Symbol	Values		Unit	Note
		Min.	Max.		
Operating temperature (ambient)	$T_{OPR}$	0	+65	°C	
Storage Temperature	$T_{STG}$	-50	+100	°C	<sup>1)</sup>
Barometric Pressure (operating & storage)	PBar	+69	+105	kPa	<sup>2)</sup>
Operating Humidity (relative)	$H_{OPR}$	10	90	%	
Storage Humidity (without condensation)	$H_{STG}$	5	95	%	

1) Storage Temperature is the case surface temperature on the center/top side of the DRAM.

2) Up to 3000 m.



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

**TABLE 10**  
**DRAM Component Operating Temperature Range**

Symbol	Parameter	Rating		Unit	Note
		Min.	Max.		
$T_{CASE}$	Operating Temperature	0	95	°C	1)2)3)4)

- 1) Operating Temperature is the case surface temperature on the center / top side of the DRAM.
- 2) The operating temperature range are the temperatures where all DRAM specification will be supported. During operation, the DRAM case temperature must be maintained between 0 - 95 °C under all other specification parameters.
- 3) Above 85 °C the Auto-Refresh command interval has to be reduced to  $t_{REFI} = 3.9 \mu s$
- 4) When operating this product in the 85 °C to 95 °C  $T_{CASE}$  temperature range, the High Temperature Self Refresh has to be enabled by setting EMR(2) bit A7 to "1". When the High Temperature Self Refresh is enabled there is an increase of  $I_{DD6}$  by approximately 50%

## 3.2 DC Operating Conditions

**TABLE 11**  
**Supply Voltage Levels and DC Operating Conditions**

Parameter	Symbol	Values			Unit	Note
		Min.	Typ.	Max.		
Device Supply Voltage	$V_{DD}$	1.7	1.8	1.9	V	
Output Supply Voltage	$V_{DDQ}$	1.7	1.8	1.9	V	1)
Input Reference Voltage	$V_{REF}$	$0.49 \times V_{DDQ}$	$0.5 \times V_{DDQ}$	$0.51 \times V_{DDQ}$	V	2)
SPD Supply Voltage	$V_{DDSPD}$	1.7	—	3.6	V	
DC Input Logic High	$V_{IH(DC)}$	$V_{REF} + 0.125$	—	$V_{DDQ} + 0.3$	V	
DC Input Logic Low	$V_{IL(DC)}$	-0.30	—	$V_{REF} - 0.125$	V	
In / Output Leakage Current	$I_L$	-5	—	5	μA	3)

- 1) Under all conditions,  $V_{DDQ}$  must be less than or equal to  $V_{DD}$
- 2) Peak to peak AC noise on  $V_{REF}$  may not exceed  $\pm 2\%$   $V_{REF}$  (DC).  $V_{REF}$  is also expected to track noise in  $V_{DDQ}$ .
- 3) Input voltage for any connector pin under test of  $0 \text{ V} \leq V_{IN} \leq V_{DDQ} + 0.3 \text{ V}$ ; all other pins at 0 V. Current is per pin



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

### 3.3 Timing Characteristics

#### 3.3.1 Speed Grade Definitions

**TABLE 12**  
Speed Grade Definition

Speed Grade		DDR2-800D		DDR2-800E		Unit	Note	
QAG Sort Name		-25F		-2.5				
CAS-RCD-RP latencies		5-5-5		6-6-6		$t_{CK}$		
Parameter		Symbol	Min.	Max.	Min.	Max.	—	
Clock Period	@ CL = 3	$t_{CK}$	5	8	5	8	ns	1)2)3)4)
	@ CL = 4	$t_{CK}$	3.75	8	3.75	8	ns	1)2)3)4)
	@ CL = 5	$t_{CK}$	2.5	8	3	8	ns	1)2)3)4)
	@ CL = 6	$t_{CK}$	2.5	8	2.5	8	ns	1)2)3)4)
Row Active Time		$t_{RAS}$	45	70k	45	70k	ns	1)2)3)4)5)
Row Cycle Time		$t_{RC}$	57.5	—	60	—	ns	1)2)3)4)
RAS-CAS-Delay		$t_{RCD}$	12.5	—	15	—	ns	1)2)3)4)
Row Precharge Time		$t_{RP}$	12.5	—	15	—	ns	1)2)3)4)

**TABLE 13**  
Speed Grade Definition

Speed Grade		DDR2-667C		DDR2-667D		DDR2-533C		DDR2-400B		Unit	Note	
QAG Sort Name		-3		-3S		-3.7		-5				
CAS-RCD-RP latencies		4-4-4		5-5-5		4-4-4		3-3-3		$t_{CK}$		
Parameter		Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	—	
Clock Period	@ CL = 3	$t_{CK}$	5	8	5	8	5	8	5	8	ns	1)2)3)4)
	@ CL = 4	$t_{CK}$	3	8	3.75	8	3.75	8	5	8	ns	1)2)3)4)
	@ CL = 5	$t_{CK}$	3	8	3	8	3.75	8	5	8	ns	1)2)3)4)
Row Active Time		$t_{RAS}$	45	70k	45	70k	45	70k	40	70k	ns	1)2)3)4)5)
Row Cycle Time		$t_{RC}$	57	—	60	—	60	—	55	—	ns	1)2)3)4)
RAS-CAS-Delay		$t_{RCD}$	12	—	15	—	15	—	15	—	ns	1)2)3)4)
Row Precharge Time		$t_{RP}$	12	—	15	—	15	—	15	—	ns	1)2)3)4)

1) Timings are guaranteed with CK/CK differential Slew Rate of 2.0 V/ns. For DQS signals timings are guaranteed with a differential Slew Rate of 2.0 V/ns in differential strobe mode and a Slew Rate of 1 V/ns in single ended mode. Timings are further guaranteed for normal OCD drive strength (EMRS(1) A1 = 0) mentioned in Component datasheet.

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

- 2) The CK/ $\overline{CK}$  input reference level (for timing reference to CK/ $\overline{CK}$ ) is the point at which CK and  $\overline{CK}$  cross. The DQS /  $\overline{DQS}$ , RDQS /  $\overline{RDQS}$ , input reference level is the crosspoint when in differential strobe mode
- 3) Inputs are not recognized as valid until  $V_{REF}$  stabilizes. During the period before  $V_{REF}$  stabilizes, CKE =  $0.2 \times V_{DDQ}$
- 4) The output timing reference voltage level is  $V_{TT}$ .
- 5)  $t_{RAS,MAX}$  is calculated from the maximum amount of time a DDR2 device can operate without a refresh command which is equal to  $9 \times t_{REFI}$ .

### 3.3.2 Component AC Timing Parameters

TABLE 14

DRAM Component Timing Parameter by Speed Grade - DDR2-800 and DDR2-667

Parameter	Symbol	DDR2-800		DDR2-667		Unit	Note <sup>2)(3)5 (6)(7)(8)</sup>
		Min.	Max.	Min.	Max.		
CAS to CAS command delay	$t_{CCD}$	2	—	2	—	nCK	
Average clock high pulse width	$t_{CH.AVG}$	0.48	0.52	0.48	0.52	$t_{CK.AVG}$	10)11)
Average clock period	$t_{CK.AVG}$	2500	8000	3000	8000	ps	
CKE minimum pulse width ( high and low pulse width)	$t_{CKE}$	3	—	3	—	nCK	12)
Average clock low pulse width	$t_{CL.AVG}$	0.48	0.52	0.48	0.52	$t_{CK.AVG}$	10)11)
Auto-Precharge write recovery + precharge time	$t_{DAL}$	WR + $t_{nRP}$	—	WR + $t_{nRP}$	—	nCK	13)14)
Minimum time clocks remain ON after CKE asynchronously drops LOW	$t_{DELAY}$	$t_{IS} + t_{CK.AVG} + t_{IH}$	—	$t_{IS} + t_{CK.AVG} + t_{IH}$	—	ns	
DQ and DM input hold time	$t_{DH.BASE}$	125	—	175	—	ps	15)19)20)
DQ and DM input pulse width for each input	$t_{DIPW}$	0.35	—	0.35	—	$t_{CK.AVG}$	
DQS input high pulse width	$t_{DQSH}$	0.35	—	0.35	—	$t_{CK.AVG}$	
DQS input low pulse width	$t_{DQSL}$	0.35	—	0.35	—	$t_{CK.AVG}$	
DQS-DQ skew for DQS & associated DQ signals	$t_{DQSQ}$	—	200	—	240	ps	16)
DQS latching rising transition to associated clock edges	$t_{DQSS}$	- 0.25	+ 0.25	- 0.25	+ 0.25	$t_{CK.AVG}$	17)
DQ and DM input setup time	$t_{DS.BASE}$	50	—	100	—	ps	18)19)20)
DQS falling edge hold time from CK	$t_{DSH}$	0.2	—	0.2	—	$t_{CK.AVG}$	17)
DQS falling edge to CK setup time	$t_{DSS}$	0.2	—	0.2	—	$t_{CK.AVG}$	17)
CK half pulse width	$t_{HP}$	Min( $t_{CH.ABS}$ , $t_{CL.ABS}$ )	—	Min( $t_{CH.ABS}$ , $t_{CL.ABS}$ )	—	ps	21)
Data-out high-impedance time from CK / $\overline{CK}$	$t_{HZ}$	—	$t_{AC.MAX}$	—	$t_{AC.MAX}$	ps	9)22)
Address and control input hold time	$t_{IH.BASE}$	250	—	275	—	ps	23)25)
Control & address input pulse width for each input	$t_{IPW}$	0.6	—	0.6	—	$t_{CK.AVG}$	
Address and control input setup time	$t_{IS.BASE}$	175	—	200	—	ps	24)25)
DQ low impedance time from CK/ $\overline{CK}$	$t_{LZ.DQ}$	$2 \times t_{AC.MIN}$	$t_{AC.MAX}$	$2 \times t_{AC.MIN}$	$t_{AC.MAX}$	ps	9)22)

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Parameter	Symbol	DDR2-800		DDR2-667		Unit	Note <sup>2)3)5) 6)7)8)</sup>
		Min.	Max.	Min.	Max.		
DQS/DQS low-impedance time from CK / CK	$t_{LZ,DQS}$	$t_{AC,MIN}$	$t_{AC,MAX}$	$t_{AC,MIN}$	$t_{AC,MAX}$	ps	9)22)
MRS command to ODT update delay	$t_{MOD}$	0	12	0	12	ns	35)
Mode register set command cycle time	$t_{MRD}$	2	—	2	—	nCK	
OCD drive mode output delay	$t_{OIT}$	0	12	0	12	ns	35)
DQ/DQS output hold time from DQS	$t_{QH}$	$t_{HP} - t_{QHS}$	—	$t_{HP} - t_{QHS}$	—	ps	26)
DQ hold skew factor	$t_{QHS}$	—	300	—	340	ps	27)
Average periodic refresh Interval	$t_{REFI}$	—	7.8	—	7.8	$\mu$ s	28)29)
		—	3.9	—	3.9	$\mu$ s	28)30)
Auto-Refresh to Active/Auto-Refresh command period	$t_{RFC}$	105	—	105	—	ns	31)
Precharge-All (4 banks) command period	$t_{RP}$	$t_{RP}$	—	$t_{RP}$	—	ns	
Read preamble	$t_{RPRE}$	0.9	1.1	0.9	1.1	$t_{CK,AVG}$	32)33)
Read postamble	$t_{RPST}$	0.4	0.6	0.4	0.6	$t_{CK,AVG}$	32)34)
Active to active command period for 1KB page size products	$t_{RRD}$	7.5	—	7.5	—	ns	35)
Active to active command period for 2KB page size products	$t_{RRD}$	10	—	10	—	ns	35)
Internal Read to Precharge command delay	$t_{RTP}$	7.5	—	7.5	—	ns	35)
Write preamble	$t_{WPRE}$	0.35	—	0.35	—	$t_{CK,AVG}$	
Write postamble	$t_{WPST}$	0.4	0.6	0.4	0.6	$t_{CK,AVG}$	
Write recovery time	$t_{WR}$	15	—	15	—	ns	35)
Internal write to read command delay	$t_{WTR}$	7.5	—	7.5	—	ns	35)36)
Exit power down to read command	$t_{XARD}$	2	—	2	—	nCK	
Exit active power-down mode to read command (slow exit, lower power)	$t_{XARDS}$	8 – AL	—	7 – AL	—	nCK	
Exit precharge power-down to any valid command (other than NOP or Deselect)	$t_{XP}$	2	—	2	—	nCK	
Exit self-refresh to a non-read command	$t_{XSNR}$	$t_{RFC} + 10$	—	$t_{RFC} + 10$	—	ns	35)
Exit self-refresh to read command	$t_{XSRD}$	200	—	200	—	nCK	
Write command to DQS associated clock edges	WL	RL – 1		RL-1		nCK	

1) For details and notes see the relevant Qimonda component data sheet

2)  $V_{DDQ} = 1.8 \text{ V} \pm 0.1\text{V}$ ;  $V_{DD} = 1.8 \text{ V} \pm 0.1 \text{ V}$ .

3) Timing that is not specified is illegal and after such an event, in order to guarantee proper operation, the DRAM must be powered down and then restarted through the specified initialization sequence before normal operation can continue.

4) Timings are guaranteed with CK/CK differential Slew Rate of 2.0 V/ns. For DQS signals timings are guaranteed with a differential Slew Rate of 2.0 V/ns in differential strobe mode and a Slew Rate of 1 V/ns in single ended mode.

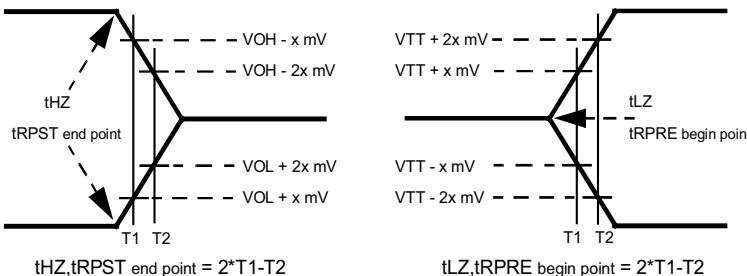
HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

- 5) The CK /  $\overline{CK}$  input reference level (for timing reference to CK /  $\overline{CK}$ ) is the point at which CK and  $\overline{CK}$  cross. The DQS /  $\overline{DQS}$ , RDQS /  $\overline{RDQS}$ , input reference level is the crosspoint when in differential strobe mode. component
- 6) Inputs are not recognized as valid until  $V_{REF}$  stabilizes. During the period before  $V_{REF}$  stabilizes, CKE =  $0.2 \times V_{DDQ}$  is recognized as low.
- 7) The output timing reference voltage level is  $V_{TT}$ . component datasheet
- 8) New units, ' $t_{CK.AVG}$ ' and 'nCK', are introduced in DDR2-667 and DDR2-800. Unit ' $t_{CK.AVG}$ ' represents the actual  $t_{CK.AVG}$  of the input clock under operation. Unit 'nCK' represents one clock cycle of the input clock, counting the actual clock edges. Note that in DDR2-400 and DDR2-533, 't<sub>CK</sub>' is used for both concepts. Example:  $t_{XP} = 2$  [nCK] means; if Power Down exit is registered at Tm, an Active command may be registered at Tm + 2, even if (Tm + 2 - Tm) is  $2 \times t_{CK.AVG} + t_{ERR.2PER(Min)}$ .
- 9) When the device is operated with input clock jitter, this parameter needs to be derated by the actual  $t_{ERR(6-10per)}$  of the input clock. (output deratings are relative to the SDRAM input clock.) For example, if the measured jitter into a DDR2-667 SDRAM has  $t_{ERR(6-10PER).MIN} = -272$  ps and  $t_{ERR(6-10PER).MAX} = +293$  ps, then  $t_{DQCK.MIN(DERATED)} = t_{DQCK.MIN} - t_{ERR(6-10PER).MAX} = -400$  ps - 293 ps = -693 ps and  $t_{DQCK.MAX(DERATED)} = t_{DQCK.MAX} - t_{ERR(6-10PER).MIN} = 400$  ps + 272 ps = +672 ps. Similarly,  $t_{LZ.DQ}$  for DDR2-667 derates to  $t_{LZ.DQ.MIN(DERATED)} = -900$  ps - 293 ps = -1193 ps and  $t_{LZ.DQ.MAX(DERATED)} = 450$  ps + 272 ps = +722 ps. (Caution on the MIN/MAX usage!)
- 10) Input clock jitter spec parameter. These parameters component datasheet are referred to as 'input clock jitter spec parameters' and these parameters apply to DDR2-667 and DDR2-800 only. The jitter specified is a random jitter meeting a Gaussian distribution.
- 11) These parameters are specified per their average values, however it is understood that the relationship component datasheet between the average timing and the absolute instantaneous timing holds all the times (min. and max of SPEC values are to be used for calculations component datasheet).
- 12)  $t_{CKE,MIN}$  of 3 clocks means CKE must be registered on three consecutive positive clock edges. CKE must remain at the valid input level the entire time it takes to achieve the 3 clocks of registration. Thus, after any CKE transition, CKE may not transition from its valid level during the time period of  $t_{IS} + 2 \times t_{CK} + t_{IH}$ .
- 13) DAL = WR + RU{ $t_{RP}(ns) / t_{CK}(ns)$ }, where RU stands for round up. WR refers to the tWR parameter stored in the MRS. For  $t_{RP}$ , if the result of the division is not already an integer, round up to the next highest integer.  $t_{CK}$  refers to the application clock period. Example: For DDR2-533 at  $t_{CK} = 3.75$  ns with  $t_{WR}$  programmed to 4 clocks.  $t_{DAL} = 4 + (15 \text{ ns} / 3.75 \text{ ns}) \text{ clocks} = 4 + (4) \text{ clocks} = 8 \text{ clocks}$ .
- 14)  $t_{DAL,nCK} = WR$  [nCK] +  $t_{nRP,nCK} = WR + RU\{t_{RP} [\text{ps}] / t_{CK.AVG}[\text{ps}]\}$ , where WR is the value programmed in the EMR.
- 15) Input waveform timing  $t_{DH}$  with differential data strobe enabled MR[bit10] = 0, is referenced from the differential data strobe crosspoint to the input signal crossing at the  $V_{IH,DC}$  level for a falling signal and from the differential data strobe crosspoint to the input signal crossing at the  $V_{IL,DC}$  level for a rising signal applied to the device under test. DQS, DQS signals must be monotonic between  $V_{IL,DC,MAX}$  and  $V_{IH,DC,MIN}$ . See **Figure 3**.
- 16)  $t_{DQSQ}$ : Consists of data pin skew and output pattern effects, and p-channel to n-channel variation of the output drivers as well as output slew rate mismatch between DQS / DQS and associated DQ in any given cycle.
- 17) These parameters are measured from a data strobe signal ((L/U/R)DQS / DQS) crossing to its respective clock signal (CK /  $\overline{CK}$ ) crossing. The spec values are not affected by the amount of clock jitter applied (i.e.  $t_{JIT.PER}$ ,  $t_{JIT.CC}$ , etc.), as these are relative to the clock signal crossing. That is, these parameters should be met whether clock jitter is present or not.
- 18) Input waveform timing  $t_{DS}$  with differential data strobe enabled MR[bit10] = 0, is referenced from the input signal crossing at the  $V_{IH,AC}$  level to the differential data strobe crosspoint for a rising signal, and from the input signal crossing at the  $V_{IL,AC}$  level to the differential data strobe crosspoint for a falling signal applied to the device under test. DQS, DQS signals must be monotonic between  $V_{il(DC)MAX}$  and  $V_{ih(DC)MIN}$ . See **Figure 3**.
- 19) If  $t_{DS}$  or  $t_{DH}$  is violated, data corruption may occur and the data must be re-written with valid data before a valid READ can be executed.
- 20) These parameters are measured from a data signal ((L/U)DM, (L/U)DQ0, (L/U)DQ1, etc.) transition edge to its respective data strobe signal ((L/U/R)DQS / DQS) crossing.
- 21)  $t_{HP}$  is the minimum of the absolute half period of the actual input clock.  $t_{HP}$  is an input parameter but not an input specification parameter. It is used in conjunction with  $t_{QHS}$  to derive the DRAM output timing  $t_{QH}$ . The value to be used for  $t_{QH}$  calculation is determined by the following equation;  $t_{HP} = \text{MIN}(t_{CH.ABS}, t_{CL.ABS})$ , where,  $t_{CH.ABS}$  is the minimum of the actual instantaneous clock high time;  $t_{CL.ABS}$  is the minimum of the actual instantaneous clock low time.
- 22)  $t_{HZ}$  and  $t_{LZ}$  transitions occur in the same access time as valid data transitions. These parameters are referenced to a specific voltage level which specifies when the device output is no longer driving ( $t_{HZ}$ ), or begins driving ( $t_{LZ}$ ).
- 23) Input waveform timing is referenced from the input signal crossing at the  $V_{IL,DC}$  level for a rising signal and  $V_{IH,DC}$  for a falling signal applied to the device under test. See **Figure 4**.
- 24) Input waveform timing is referenced from the input signal crossing at the  $V_{IH,AC}$  level for a rising signal and  $V_{IL,AC}$  for a falling signal applied to the device under test. See **Figure 4**.
- 25) These parameters are measured from a command/address signal (CKE, CS, RAS, CAS, WE, ODT, BA0, A0, A1, etc.) transition edge to its respective clock signal (CK /  $\overline{CK}$ ) crossing. The spec values are not affected by the amount of clock jitter applied (i.e.  $t_{JIT.PER}$ ,  $t_{JIT.CC}$ , etc.), as the setup and hold are relative to the clock signal crossing that latches the command/address. That is, these parameters should be met whether clock jitter is present or not.
- 26)  $t_{QH} = t_{HP} - t_{QHS}$ , where:  $t_{HP}$  is the minimum of the absolute half period of the actual input clock; and  $t_{QHS}$  is the specification value under the max column. {The less half-pulse width distortion present, the larger the  $t_{QH}$  value is; and the larger the valid data eye will be.} Examples: 1) If the system provides  $t_{HP}$  of 1315 ps into a DDR2-667 SDRAM, the DRAM provides  $t_{QH}$  of 975 ps minimum. 2) If the system provides  $t_{HP}$  of 1420 ps into a DDR2-667 SDRAM, the DRAM provides  $t_{QH}$  of 1080 ps minimum.

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

- 27)  $t_{QHS}$  accounts for: 1) The pulse duration distortion of on-chip clock circuits, which represents how well the actual  $t_{HP}$  at the input is transferred to the output; and 2) The worst case push-out of DQS on one transition followed by the worst case pull-in of DQ on the next transition, both of which are independent of each other, due to data pin skew, output pattern effects, and pchannel to n-channel variation of the output drivers.
- 28) The Auto-Refresh command interval has been reduced to 3.9  $\mu$ s when operating the DDR2 DRAM in a temperature range between 85 °C and 95 °C.
- 29)  $0^{\circ}\text{C} \leq T_{\text{CASE}} \leq 85^{\circ}\text{C}$ .
- 30)  $85^{\circ}\text{C} < T_{\text{CASE}} \leq 95^{\circ}\text{C}$ .
- 31) A maximum of eight Auto-Refresh commands can be posted to any given DDR2 SDRAM device.
- 32)  $t_{RPST}$  end point and  $t_{RPRE}$  begin point are not referenced to a specific voltage level but specify when the device output is no longer driving ( $t_{RPST}$ ), or begins driving ( $t_{RPRE}$ ). **Figure 2** shows a method to calculate these points when the device is no longer driving ( $t_{RPST}$ ), or begins driving ( $t_{RPRE}$ ) by measuring the signal at two different voltages. The actual voltage measurement points are not critical as long as the calculation is consistent.
- 33) When the device is operated with input clock jitter, this parameter needs to be derated by the actual  $t_{JIT,PER}$  of the input clock. (output deratings are relative to the SDRAM input clock.) For example, if the measured jitter into a DDR2-667 SDRAM has  $t_{JIT,PER,MIN} = -72$  ps and  $t_{JIT,PER,MAX} = +93$  ps, then  $t_{RPRE,MIN(\text{DERATED})} = t_{RPRE,MIN} + t_{JIT,PER,MIN} = 0.9 \times t_{CK,\text{AVG}} - 72$  ps = +2178 ps and  $t_{RPRE,MAX(\text{DERATED})} = t_{RPRE,MAX} + t_{JIT,PER,MAX} = 1.1 \times t_{CK,\text{AVG}} + 93$  ps = +2843 ps. (Caution on the MIN/MAX usage!).
- 34) When the device is operated with input clock jitter, this parameter needs to be derated by the actual  $t_{JIT,DUTY}$  of the input clock. (output deratings are relative to the SDRAM input clock.) For example, if the measured jitter into a DDR2-667 SDRAM has  $t_{JIT,DUTY,MIN} = -72$  ps and  $t_{JIT,DUTY,MAX} = +93$  ps, then  $t_{RPST,MIN(\text{DERATED})} = t_{RPST,MIN} + t_{JIT,DUTY,MIN} = 0.4 \times t_{CK,\text{AVG}} - 72$  ps = +928 ps and  $t_{RPST,MAX(\text{DERATED})} = t_{RPST,MAX} + t_{JIT,DUTY,MAX} = 0.6 \times t_{CK,\text{AVG}} + 93$  ps = +1592 ps. (Caution on the MIN/MAX usage!).
- 35) For these parameters, the DDR2 SDRAM device is characterized and verified to support  $t_{nPARAM} = RU\{t_{PARAM} / t_{CK,\text{AVG}}\}$ , which is in clock cycles, assuming all input clock jitter specifications are satisfied. For example, the device will support  $t_{nRP} = RU\{t_{RP} / t_{CK,\text{AVG}}\}$ , which is in clock cycles, if all input clock jitter specifications are met. This means: For DDR2-667 5-5-5, of which  $t_{RP} = 15$  ns, the device will support  $t_{nRP} = RU\{t_{RP} / t_{CK,\text{AVG}}\} = 5$ , i.e. as long as the input clock jitter specifications are met, Precharge command at Tm and Active command at Tm + 5 is valid even if (Tm + 5 - Tm) is less than 15 ns due to input clock jitter.
- 36)  $t_{WTR}$  is at least two clocks ( $2 \times t_{CK}$ ) independent of operation frequency.

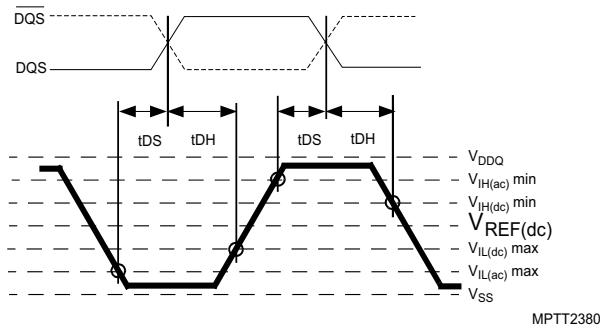
**FIGURE 2**  
Method for calculating transitions and endpoint



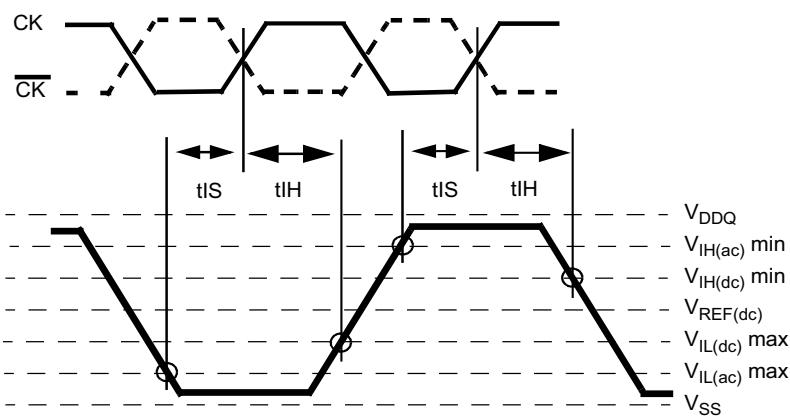


HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

**FIGURE 3**  
Differential input waveform timing  $t_{DS}$  and  $t_{DH}$



**FIGURE 4**  
Differential input waveform timing  $t_{IS}$  and  $t_{IH}$





HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

**TABLE 15**  
**DRAM Component Timing Parameter by Speed Grade - DDR2-533 and DDR2-400**

Parameter	Symbol	DDR2-533		DDR2-400		Unit	Notes <sup>2)3) 4)5)6)7)</sup>
		Min.	Max.	Min.	Max.		
CAS A to CAS B command period	$t_{CCD}$	2	—	2	—	$t_{CK}$	
CK, CK high-level width	$t_{CH}$	0.45	0.55	0.45	0.55	$t_{CK}$	
CKE minimum high and low pulse width	$t_{CKE}$	3	—	3	—	$t_{CK}$	
CK, CK low-level width	$t_{CL}$	0.45	0.55	0.45	0.55	$t_{CK}$	
Auto-Precharge write recovery + precharge time	$t_{DAL}$	WR + $t_{RP}$	—	WR + $t_{RP}$	—	$t_{CK}$	8)
Minimum time clocks remain ON after CKE asynchronously drops LOW	$t_{DELAY}$	$t_{IS} + t_{CK} + t_{IH}$	—	$t_{IS} + t_{CK} + t_{IH}$	—	ns	9)
DQ and DM input hold time (differential data strobe)	$t_{DH.BASE}$	225	—	275	—	ps	10)
DQ and DM input hold time (single ended data strobe)	$t_{DH1.BASE}$	-25	—	25	—	ps	11)
DQ and DM input pulse width (each input)	$t_{DIPW}$	0.35	—	0.35	—	$t_{CK}$	
DQS input HIGH pulse width (write cycle)	$t_{DQSH}$	0.35	—	0.35	—	$t_{CK}$	
DQS input LOW pulse width (write cycle)	$t_{DQL}$	0.35	—	0.35	—	$t_{CK}$	
DQS-DQ skew (for DQS & associated DQ signals)	$t_{DQSQ}$	—	300	—	350	ps	11)
Write command to 1st DQS latching transition	$t_{DQSS}$	- 0.25	+ 0.25	- 0.25	+ 0.25	$t_{CK}$	
DQ and DM input setup time (differential data strobe)	$t_{DS.BASE}$	100	—	150	—	ps	11)
DQ and DM input setup time (single ended data strobe)	$t_{DS1.BASE}$	-25	—	25	—	ps	11)
DQS falling edge hold time from CK (write cycle)	$t_{DSH}$	0.2	—	0.2	—	$t_{CK}$	
DQS falling edge to CK setup time (write cycle)	$t_{DSS}$	0.2	—	0.2	—	$t_{CK}$	
Four Activate Window period	$t_{FAW}$	37.5	—	37.5	—	ns	
Four Activate Window period	$t_{FAW}$	50	—	50	—	ns	13)
Clock half period	$t_{HP}$	MIN. ( $t_{CL}, t_{CH}$ )		MIN. ( $t_{CL}, t_{CH}$ )			12)
Data-out high-impedance time from CK / CK	$t_{HZ}$	—	$t_{AC.MAX}$	—	$t_{AC.MAX}$	ps	13)
Address and control input hold time	$t_{IH.BASE}$	375	—	475	—	ps	11)
Address and control input pulse width (each input)	$t_{IPW}$	0.6	—	0.6	—	$t_{CK}$	

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Parameter	Symbol	DDR2-533		DDR2-400		Unit	Notes <sup>2)3) 4)5)6)7)</sup>
		Min.	Max.	Min.	Max.		
Address and control input setup time	$t_{IS.BASE}$	250	—	350	—	ps	11)
DQ low-impedance time from CK / $\overline{CK}$	$t_{LZ(DQ)}$	$2 \times t_{AC.MIN}$	$t_{AC.MAX}$	$2 \times t_{AC.MIN}$	$t_{AC.MAX}$	ps	14)
DQS low-impedance from CK / $\overline{CK}$	$t_{LZ(DQS)}$	$t_{AC.MIN}$	$t_{AC.MAX}$	$t_{AC.MIN}$	$t_{AC.MAX}$	ps	14)
MRS command to ODT update delay	$t_{MOD}$	0	12	0	12	ns	
Mode register set command cycle time	$t_{MRD}$	2	—	2	—	$t_{CK}$	
OCD drive mode output delay	$t_{OIT}$	0	12	0	12	ns	
Data output hold time from DQS	$t_{QH}$	$t_{HP} - t_{QHS}$	—	$t_{HP} - t_{QHS}$	—		
Data hold skew factor	$t_{QHS}$	—	400	—	450	ps	
Average periodic refresh Interval	$t_{REFI}$	—	7.8	—	7.8	$\mu s$	14)15)
Average periodic refresh Interval	$t_{REFI}$	—	3.9	—	3.9	$\mu s$	16)18)
Auto-Refresh to Active/Auto-Refresh command period	$t_{RFC}$	105	—	105	—	ns	17)
Precharge-All (4 banks) command period	$t_{RP}$	$t_{RP}$	—	$t_{RP}$	—	ns	
Read preamble	$t_{RPRE}$	0.9	1.1	0.9	1.1	$t_{CK}$	14)
Read postamble	$t_{RPST}$	0.40	0.60	0.40	0.60	$t_{CK}$	14)
Active bank A to Active bank B command period	$t_{RRD}$	7.5	—	7.5	—	ns	14)18)
Active bank A to Active bank B command period	$t_{RRD}$	10	—	10	—	ns	16)22)
Internal Read to Precharge command delay	$t_{RTP}$	7.5	—	7.5	—	ns	
Write preamble	$t_{WPRE}$	0.25	—	0.25	—	$t_{CK}$	
Write postamble	$t_{WPST}$	0.40	0.60	0.40	0.60	$t_{CK}$	19)
Write recovery time for write without Auto-Precharge	$t_{WR}$	15	—	15	—	ns	
Internal Write to Read command delay	$t_{WTR}$	7.5	—	10	—	ns	20)
Exit power down to any valid command (other than NOP or Deselect)	$t_{XARD}$	2	—	2	—	$t_{CK}$	21)
Exit active power-down mode to Read command (slow exit, lower power)	$t_{XARDS}$	6 – AL	—	6 – AL	—	$t_{CK}$	21)
Exit precharge power-down to any valid command (other than NOP or Deselect)	$t_{XP}$	2	—	2	—	$t_{CK}$	
Exit Self-Refresh to non-Read command	$t_{XSNR}$	$t_{RFC} + 10$	—	$t_{RFC} + 10$	—	ns	

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Parameter	Symbol	DDR2-533		DDR2-400		Unit	Notes <sup>2)3)</sup> 4)5)6)7)
		Min.	Max.	Min.	Max.		
Exit Self-Refresh to Read command	$t_{XSRD}$	200	—	200	—	$t_{CK}$	
Write recovery time for write with Auto-Precharge	WR	$t_{WR}/t_{CK}$		$t_{WR}/t_{CK}$		$t_{CK}$	22)

- 1) For details and notes see the relevant Qimonda component data sheet
- 2)  $V_{DDQ} = 1.8 \text{ V} \pm 0.1\text{V}$ ;  $V_{DD} = 1.8 \text{ V} \pm 0.1 \text{ V}$ .
- 3) Timing that is not specified is illegal and after such an event, in order to guarantee proper operation, the DRAM must be powered down and then restarted through the specified initialization sequence before normal operation can continue.
- 4) Timings are guaranteed with CK/ $\overline{CK}$  differential Slew Rate of 2.0 V/ns. For DQS signals timings are guaranteed with a differential Slew Rate of 2.0 V/ns in differential strobe mode and a Slew Rate of 1 V/ns in single ended mode.
- 5) The CK /  $\overline{CK}$  input reference level (for timing reference to CK /  $\overline{CK}$ ) is the point at which CK and  $\overline{CK}$  cross. The DQS /  $\overline{DQS}$ , RDQS /  $\overline{RDQS}$ , input reference level is the crosspoint when in differential strobe mode. component
- 6) Inputs are not recognized as valid until  $V_{REF}$  stabilizes. During the period before  $V_{REF}$  stabilizes,  $CKE = 0.2 \times V_{DDQ}$  is recognized as low.
- 7) The output timing reference voltage level is  $V_{TT}$ . component datasheet
- 8) For each of the terms, if not already an integer, round to the next highest integer.  $t_{CK}$  refers to the application clock period. WR refers to the WR parameter stored in the MR.
- 9) The clock frequency is allowed to change during self-refresh mode or precharge power-down mode.
- 10) For timing definition, refer to the Component data sheet.
- 11) Consists of data pin skew and output pattern effects, and p-channel to n-channel variation of the output drivers as well as output Slew Rate mis-match between DQS /  $\overline{DQS}$  and associated DQ in any given cycle.
- 12) MIN ( $t_{CL}$ ,  $t_{CH}$ ) refers to the smaller of the actual clock low time and the actual clock high time as provided to the device (i.e. this value can be greater than the minimum specification limits for  $t_{CL}$  and  $t_{CH}$ ).
- 13) The  $t_{HZ}$ ,  $t_{RPST}$  and  $t_{LZ}$ ,  $t_{RPRE}$  parameters are referenced to a specific voltage level, which specify when the device output is no longer driving ( $t_{HZ}$ ,  $t_{RPST}$ ), or begins driving ( $t_{LZ}$ ,  $t_{RPRE}$ ).  $t_{HZ}$  and  $t_{LZ}$  transitions occur in the same access time windows as valid data transitions. These parameters are verified by design and characterization, but not subject to production test.
- 14) The Auto-Refresh command interval has to be reduced to 3.9  $\mu\text{s}$  when operating the DDR2 DRAM in a temperature range between 85 °C and 95 °C.
- 15)  $0 \text{ }^{\circ}\text{C} \leq T_{CASE} \leq 85 \text{ }^{\circ}\text{C}$ .
- 16)  $85 \text{ }^{\circ}\text{C} < T_{CASE} \leq 95 \text{ }^{\circ}\text{C}$ .
- 17) A maximum of eight Auto-Refresh commands can be posted to any given DDR2 SDRAM device
- 18) The  $t_{RRD}$  timing parameter depends on the page size of the DRAM organization.
- 19) The maximum limit for the  $t_{WPST}$  parameter is not a device limit. The device operates with a greater value for this parameter, but system performance (bus turnaround) degrades accordingly.
- 20) Minimum  $t_{WTR}$  is two clocks when operating the DDR2-SDRAM at frequencies  $\leq 200 \text{ MHz}$ .
- 21) User can choose two different active power-down modes for additional power saving via MRS address bit A12. In "standard active power-down mode" (MR, A12 = "0") a fast power-down exit timing  $t_{XARD}$  can be used. In "low active power-down mode" (MR, A12 = "1") a slow power-down exit timing  $t_{XARDS}$  has to be satisfied.
- 22) WR must be programmed to fulfill the minimum requirement for the  $t_{WR}$  timing parameter, where  $WR_{MIN[\text{cycles}]} = t_{WR}(\text{ns})/t_{CK}(\text{ns})$  rounded up to the next integer value.  $t_{DAL} = WR + (t_{RP}/t_{CK})$ . For each of the terms, if not already an integer, round to the next highest integer.  $t_{CK}$  refers to the application clock period. WR refers to the WR parameter stored in the MRS.



### 3.3.3 ODT AC Electrical Characteristics

This chapter describes the ODT AC electrical characteristics.

**TABLE 16**  
**ODT AC Characteristics and Operating Conditions for DDR2-667 & DDR2-800**

Symbol	Parameter / Condition	Values		Unit	Note
		Min.	Max.		
$t_{AOND}$	ODT turn-on delay	2	2	$n_{CK}$	<sup>1)</sup>
$t_{AON}$	ODT turn-on	$t_{AC,MIN}$	$t_{AC,MAX} + 0.7$ ns	ns	<sup>1,2)</sup>
$t_{AONPD}$	ODT turn-on (Power-Down Modes)	$t_{AC,MIN} + 2$ ns	$2 t_{CK} + t_{AC,MAX} + 1$ ns	ns	<sup>1)</sup>
$t_{AOFD}$	ODT turn-off delay	2.5	2.5	$n_{CK}$	<sup>1)</sup>
$t_{AOF}$	ODT turn-off	$t_{AC,MIN}$	$t_{AC,MAX} + 0.6$ ns	ns	<sup>1,3)</sup>
$t_{AOFPD}$	ODT turn-off (Power-Down Modes)	$t_{AC,MIN} + 2$ ns	$2.5 t_{CK} + t_{AC,MAX} + 1$ ns	ns	<sup>1)</sup>
$t_{ANPD}$	ODT to Power Down Mode Entry Latency	3	—	$n_{CK}$	<sup>1)</sup>
$t_{AXPD}$	ODT Power Down Exit Latency	8	—	$n_{CK}$	<sup>1)</sup>

- 1) New units, " $t_{CK,AVG}$ " and " $n_{CK}$ ", are introduced in DDR2-667 and DDR2-800. Unit " $t_{CK,AVG}$ " represents the actual  $t_{CK,AVG}$  of the input clock under operation. Unit " $n_{CK}$ " represents one clock cycle of the input clock, counting the actual clock edges. Note that in DDR2-400 and DDR2-533, " $t_{CK}$ " is used for both concepts. Example:  $t_{XP} = 2 [n_{CK}]$  means; if Power Down exit is registered at  $T_m$ , an Active command may be registered at  $T_m + 2$ , even if  $(T_m + 2 - T_m)$  is  $2 \times t_{CK,Avg} + t_{ERR,2PER(Min)}$ .
- 2) ODT turn on time min is when the device leaves high impedance and ODT resistance begins to turn on. ODT turn on time max is when the ODT resistance is fully on. Both are measured from  $t_{AOND}$ , which is interpreted differently per speed bin. For DDR2-667/800,  $t_{AOND}$  is 2 clock cycles after the clock edge that registered a first ODT HIGH counting the actual input clock edges.
- 3) ODT turn off time min is when the device starts to turn off ODT resistance. ODT turn off time max is when the bus is in high impedance. Both are measured from  $t_{AOFD}$ , which is interpreted differently per speed bin. For DDR2-667/800, if  $t_{CK,avg} = 3$  ns is assumed,  $t_{AOFD}$  is 1.5 ns (=  $0.5 \times 3$  ns) after the second trailing clock edge counting from the clock edge that registered a first ODT LOW and by counting the actual input clock edges.

**TABLE 17**  
**ODT AC Characteristics and Operating Conditions for DDR2-533 & DDR2-400**

Symbol	Parameter / Condition	Values		Unit	Note
		Min.	Max.		
$t_{AOND}$	ODT turn-on delay	2	2	$t_{CK}$	
$t_{AON}$	ODT turn-on	$t_{AC,MIN}$	$t_{AC,MAX} + 1$ ns	ns	<sup>1)</sup>
$t_{AONPD}$	ODT turn-on (Power-Down Modes)	$t_{AC,MIN} + 2$ ns	$2 t_{CK} + t_{AC,MAX} + 1$ ns	ns	
$t_{AOFD}$	ODT turn-off delay	2.5	2.5	$t_{CK}$	
$t_{AOF}$	ODT turn-off	$t_{AC,MIN}$	$t_{AC,MAX} + 0.6$ ns	ns	<sup>2)</sup>
$t_{AOFPD}$	ODT turn-off (Power-Down Modes)	$t_{AC,MIN} + 2$ ns	$2.5 t_{CK} + t_{AC,MAX} + 1$ ns	ns	
$t_{ANPD}$	ODT to Power Down Mode Entry Latency	3	—	$t_{CK}$	
$t_{AXPD}$	ODT Power Down Exit Latency	8	—	$t_{CK}$	

- 1) ODT turn on time min. is when the device leaves high impedance and ODT resistance begins to turn on. ODT turn on time max is when the ODT resistance is fully on. Both are measured from  $t_{AOND}$ , which is interpreted differently per speed bin. For DDR2-400/533,  $t_{AOND}$  is 10 ns (=  $2 \times 5$  ns) after the clock edge that registered a first ODT HIGH if  $t_{CK} = 5$  ns.

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

- 2) ODT turn off time min. is when the device starts to turn off ODT resistance. ODT turn off time max is when the bus is in high impedance. Both are measured from  $t_{AOFD}$ . Both are measured from  $t_{AOFD}$ , which is interpreted differently per speed bin. For DDR2-400/533,  $t_{AOFD}$  is 12.5 ns (= 2.5 x 5 ns) after the clock edge that registered a first ODT HIGH if  $t_{CK} = 5$  ns.

### 3.4 $I_{DD}$ Specifications and Conditions

List of tables defining  $I_{DD}$  Specifications and Conditions.

**TABLE 18**  
 **$I_{DD}$  Measurement Conditions**

Parameter	Symbol	Note <sup>1)2)</sup> <sup>3)4)5)</sup>
<b>Operating Current 0</b> One bank Active - Precharge; $t_{CK} = t_{CK.MIN}$ , $t_{RC} = t_{RC.MIN}$ , $t_{RAS} = t_{RAS.MIN}$ , CKE is HIGH, $\overline{CS}$ is HIGH between valid commands. Address and control inputs are SWITCHING, Databus inputs are SWITCHING.	$I_{DD0}$	
<b>Operating Current 1</b> One bank Active - Read - Precharge; $I_{OUT} = 0$ mA, BL = 4, $t_{CK} = t_{CK.MIN}$ , $t_{RC} = t_{RC.MIN}$ , $t_{RAS} = t_{RAS.MIN}$ , $t_{RCD} = t_{RCD.MIN}$ , AL = 0, CL = CL <sub>MIN</sub> ; CKE is HIGH, $\overline{CS}$ is HIGH between valid commands. Address and control inputs are SWITCHING, Databus inputs are SWITCHING.	$I_{DD1}$	<sup>6)</sup>
<b>Precharge Standby Current</b> All banks idle; $\overline{CS}$ is HIGH; CKE is HIGH; $t_{CK} = t_{CK.MIN}$ ; Other control and address inputs are SWITCHING, Databus inputs are SWITCHING.	$I_{DD2N}$	
<b>Precharge Power-Down Current</b> Other control and address inputs are STABLE, Data bus inputs are FLOATING.	$I_{DD2P}$	
<b>Precharge Quiet Standby Current</b> All banks idle; $\overline{CS}$ is HIGH; CKE is HIGH; $t_{CK} = t_{CK.MIN}$ ; Other control and address inputs are STABLE, Data bus inputs are FLOATING.	$I_{DD2Q}$	
<b>Active Standby Current</b> Burst Read: All banks open; Continuous burst reads; BL = 4; AL = 0, CL = CL <sub>MIN</sub> ; $t_{CK} = t_{CK.MIN}$ ; $t_{RAS} = t_{RAS.MAX}$ ; $t_{RP} = t_{RP.MIN}$ ; CKE is HIGH, $\overline{CS}$ is HIGH between valid commands. Address inputs are SWITCHING; Data Bus inputs are SWITCHING; $I_{OUT} = 0$ mA.	$I_{DD3N}$	
<b>Active Power-Down Current</b> All banks open; $t_{CK} = t_{CK.MIN}$ , CKE is LOW; Other control and address inputs are STABLE, Data bus inputs are FLOATING. MRS A12 bit is set to LOW (Fast Power-down Exit);	$I_{DD3P(0)}$	
<b>Active Power-Down Current</b> All banks open; $t_{CK} = t_{CK.MIN}$ , CKE is LOW; Other control and address inputs are STABLE, Data bus inputs are FLOATING. MRS A12 bit is set to HIGH (Slow Power-down Exit);	$I_{DD3P(1)}$	
<b>Operating Current - Burst Read</b> All banks open; Continuous burst reads; BL = 4; AL = 0, CL = CL <sub>MIN</sub> ; $t_{CK} = t_{CKMIN}$ ; $t_{RAS} = t_{RASMAX}$ ; $t_{RP} = t_{RPMIN}$ ; CKE is HIGH, CS is HIGH between valid commands; Address inputs are SWITCHING; Data bus inputs are SWITCHING; $I_{OUT} = 0$ mA.	$I_{DD4R}$	<sup>6)</sup>
<b>Operating Current - Burst Write</b> All banks open; Continuous burst writes; BL = 4; AL = 0, CL = CL <sub>MIN</sub> ; $t_{CK} = t_{CK.MIN}$ ; $t_{RAS} = t_{RAS.MAX}$ ; $t_{RP} = t_{RP.MAX}$ ; CKE is HIGH, $\overline{CS}$ is HIGH between valid commands. Address inputs are SWITCHING; Data Bus inputs are SWITCHING;	$I_{DD4W}$	
<b>Burst Refresh Current</b> $t_{CK} = t_{CK.MIN}$ , Refresh command every $t_{RFC} = t_{RFC.MIN}$ interval, CKE is HIGH, $\overline{CS}$ is HIGH between valid commands, Other control and address inputs are SWITCHING, Data bus inputs are SWITCHING.	$I_{DD5B}$	

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Parameter	Symbol	Note <sup>1)2) 3)4)5)</sup>
<b>Distributed Refresh Current</b> $t_{CK} = t_{CK,MIN.}$ , Refresh command every $t_{RFC} = t_{REFI}$ interval, CKE is LOW and $\overline{CS}$ is HIGH between valid commands, Other control and address inputs are SWITCHING, Data bus inputs are SWITCHING.	$I_{DD5D}$	
<b>Self-Refresh Current</b> CKE $\leq 0.2$ V; external clock off, CK and $\overline{CK}$ at 0 V; Other control and address inputs are FLOATING, Data bus inputs are FLOATING. $I_{DD6}$ current values are guaranteed up to $T_{CASE}$ of 85 °C max.	$I_{DD6}$	
<b>All Bank Interleave Read Current</b> All banks are being interleaved at minimum $t_{RC}$ without violating $t_{RRD}$ using a burst length of 4. Control and address bus inputs are STABLE during DESELECTS. $I_{out} = 0$ mA.	$I_{DD7}$	<sup>6)</sup>

- 1)  $V_{DDQ} = 1.8 \text{ V} \pm 0.1 \text{ V}; V_{DD} = 1.8 \text{ V} \pm 0.1 \text{ V}$
- 2)  $I_{DD}$  specifications are tested after the device is properly initialized and  $I_{DD}$  parameter are specified with ODT disabled.
- 3) Definitions for  $I_{DD}$  see **Table 19**
- 4) For two rank modules: All active current measurements in the same  $I_{DD}$  current mode. The other rank is in  $I_{DD2P}$  Precharge Power-Down Mode.
- 5) For details and notes see the relevant Qimonda component data sheet.
- 6)  $I_{DD1}, I_{DD4R}$  and  $I_{DD7}$  current measurements are defined with the outputs disabled ( $I_{OUT} = 0$  mA). To achieve this on module level the output buffers can be disabled using an EMRS(1) (Extended Mode Register Command) by setting A12 bit to HIGH.

**TABLE 19**  
Definitions for  $I_{DD}$

Parameter	Description
LOW	$V_{IN} \leq V_{IL(ac).MAX}$ , HIGH is defined as $V_{IN} \geq V_{IH(ac).MIN}$
STABLE	Inputs are stable at a HIGH or LOW level
FLOATING	Inputs are $V_{REF} = V_{DDQ}/2$
SWITCHING	Inputs are changing between HIGH and LOW every other clock (once per 2 cycles) for address and control signals, and inputs changing between HIGH and LOW every other data transfer (once per cycle) for DQ signals not including mask or strobes.



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

**TABLE 20**  
*I<sub>DD</sub>* Specification for HYS64T[32/64/128]xxxHDL-[25F/2.5]-B

Product Type	HYS64T32000HDL-25F-B	HYS64T64020HDL-25F-B	HYS64T128021HDL-25F-B	HYS64T32000HDL-2.5-B	HYS64T64020HDL-2.5-B	HYS64T128021HDL-2.5-B	Unit	Note <sup>1)</sup>
Organization	256 MB	512 MB	1 GB	256 MB	512 MB	1 GB		
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)		
	×64	×64	×64	×64	×64	×64		
	-25F	-25F	-25F	-2.5	-2.5	-2.5		
Symbol	Max.	Max.	Max.	Max.	Max.	Max.		
<i>I<sub>DD0</sub></i>	420	448	728	400	428	696	mA	2)
<i>I<sub>DD1</sub></i>	480	508	856	460	488	820	mA	2)
<i>I<sub>DD2P</sub></i>	30	60	112	28	56	110	mA	3)
<i>I<sub>DD2N</sub></i>	205	410	820	200	408	820	mA	3)
<i>I<sub>DD2Q</sub></i>	180	360	720	180	360	720	mA	3)
<i>I<sub>DD3P</sub></i> ( MRS = 0)	160	312	624	156	310	620	mA	3)
<i>I<sub>DD3P</sub></i> ( MRS = 1)	40	72	144	40	70	140	mA	4)3)
<i>I<sub>DD3N</sub></i>	240	480	960	240	480	960	mA	5)3)
<i>I<sub>DD4R</sub></i>	720	750	1300	720	748	1300	mA	2)
<i>I<sub>DD4W</sub></i>	800	830	1300	800	828	1300	mA	2)
<i>I<sub>DD5B</sub></i>	580	610	1220	580	608	1220	mA	2)
<i>I<sub>DD5D</sub></i>	40	72	144	40	70	140	mA	3)6)
<i>I<sub>DD6</sub></i>	24	40	80	24	40	80	mA	3)6)
<i>I<sub>DD7</sub></i>	1060	1088	1416	1020	1048	1340	mA	2)

1) Calculated values from component data. ODT disabled. *I<sub>DD1</sub>*, *I<sub>DD4R</sub>*, and *I<sub>DD7</sub>*, are defined with the outputs disabled.

2) The other rank is in *I<sub>DD2P</sub>* Precharge Power-Down Current mode.

3) Both ranks are in the same *I<sub>DD</sub>* current mode.

4) Fast: MRS(12)=0

5) Slow: MRS(12)=1

6) *I<sub>DD5D</sub>* and *I<sub>DD6</sub>* values are for 0°C ≤ *T<sub>Case</sub>* ≤ 85°C



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

**TABLE 21**  
 **$I_{DD}$  Specification for HYS64T[32/64/128]xxxHDL-[3/3S]-B**

Product Type	HYS64T32000HDL-3-B	HYS64T64020HDL-3-B	HYS64T128021HDL-3-B	HYS64T32000HDL-3S-B HYS64T32900HDL-3S-B	HYS64T64020HDL-3S-B HYS64T64920HDL-3S-B	HYS64T128021HDL-3S-B HYS64T128921HDL-3S-B	Unit	Note <sup>1)</sup>
Organization	256 MB	512 MB	1 GB	256 MB	512 MB	1 GB		
	1 Rank ( $\times 16$ )	2 Ranks ( $\times 16$ )	2 Ranks ( $\times 8$ )	1 Rank ( $\times 16$ )	2 Ranks ( $\times 16$ )	2 Ranks ( $\times 8$ )		
	$\times 64$	$\times 64$	$\times 64$	$\times 64$	$\times 64$	$\times 64$		
	-3	-3	-3	-3S	-3S	-3S		
Symbol	Max.	Max.	Max.	Max.	Max.	Max.		
$I_{DD0}$	380	410	660	360	390	620	mA	<sup>2)</sup>
$I_{DD1}$	420	450	780	400	430	740	mA	<sup>2)</sup>
$I_{DD2P}$	30	60	110	30	60	110	mA	<sup>3)</sup>
$I_{DD2N}$	180	360	720	180	360	720	mA	<sup>3)</sup>
$I_{DD2Q}$	160	320	640	160	320	640	mA	<sup>3)</sup>
$I_{DD3P}$ (MRS = 0)	130	260	530	130	260	530	mA	<sup>3)</sup>
$I_{DD3P}$ (MRS = 1)	40	70	140	40	70	140	mA	<sup>4)3)</sup>
$I_{DD3N}$	200	400	800	200	400	800	mA	<sup>5)3)</sup>
$I_{DD4R}$	620	650	1100	620	650	1100	mA	<sup>2)</sup>
$I_{DD4W}$	680	710	1100	680	710	1100	mA	<sup>2)</sup>
$I_{DD5B}$	560	590	1180	560	590	1180	mA	<sup>2)</sup>
$I_{DD5D}$	40	70	140	40	70	140	mA	<sup>3)6)</sup>
$I_{DD6}$	20	40	80	20	40	80	mA	<sup>3)6)</sup>
$I_{DD7}$	1010	1040	1340	960	990	1270	mA	<sup>2)</sup>

1) Calculated values from component data. ODT disabled.  $I_{DD1}$ ,  $I_{DD4R}$ , and  $I_{DD7}$ , are defined with the outputs disabled.

2) The other rank is in  $I_{DD2P}$  Precharge Power-Down Current mode.

3) Both ranks are in the same  $I_{DD}$  current mode.

4) Fast: MRS(12)=0

5) Slow: MRS(12)=1

6)  $I_{DD5D}$  and  $I_{DD6}$  values are for  $0^{\circ}\text{C} \leq T_{\text{Case}} \leq 85^{\circ}\text{C}$



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

**TABLE 22**  
 **$I_{DD}$  Specification for HYS64T[32/64/128]xxxHDL-[3.7/5]-B**

Product Type	HYS64T32000HDL-3.7-B HYS64T32900HDL-3.7-B	HYS64T64020HDL-3.7-B HYS64T64920HDL-3.7-B	HYS64T128021HDL-3.7-B HYS64T128921HDL-3.7-B	HYS64T32000HDL-5-B	HYS64T64020HDL-5-B	HYS64T128021HDL-5-B	Unit	Note <sup>1)</sup>
Organization	<b>256 MB</b>	<b>512 MB</b>	<b>1 GB</b>	<b>256 MB</b>	<b>512 MB</b>	<b>1 GB</b>		
	<b>1 Rank (<math>\times 16</math>)</b>	<b>2 Ranks (<math>\times 16</math>)</b>	<b>2 Ranks (<math>\times 8</math>)</b>	<b>1 Rank (<math>\times 16</math>)</b>	<b>2 Ranks (<math>\times 16</math>)</b>	<b>2 Ranks (<math>\times 8</math>)</b>		
	<b><math>\times 64</math></b>	<b><math>\times 64</math></b>	<b><math>\times 64</math></b>	<b><math>\times 64</math></b>	<b><math>\times 64</math></b>	<b><math>\times 64</math></b>		
	<b>-3.7</b>	<b>-3.7</b>	<b>-3.7</b>	<b>-5</b>	<b>-5</b>	<b>-5</b>		
Symbol	<b>Max.</b>	<b>Max.</b>	<b>Max.</b>	<b>Max.</b>	<b>Max.</b>	<b>Max.</b>		
$I_{DD0}$	320	350	580	300	330	540	mA	<sup>2)</sup>
$I_{DD1}$	360	390	660	330	360	620	mA	<sup>2)</sup>
$I_{DD2P}$	30	60	110	30	60	110	mA	<sup>3)</sup>
$I_{DD2N}$	150	300	610	140	270	540	mA	<sup>3)</sup>
$I_{DD2Q}$	140	280	560	130	260	510	mA	<sup>3)</sup>
$I_{DD3P}$ (MRS = 0)	110	220	450	100	190	380	mA	<sup>3)</sup>
$I_{DD3P}$ (MRS = 1)	40	70	140	40	70	140	mA	<sup>4)3)</sup>
$I_{DD3N}$	170	340	690	160	310	620	mA	<sup>5)3)</sup>
$I_{DD4R}$	520	550	940	460	490	820	mA	<sup>2)</sup>
$I_{DD4W}$	580	610	940	520	550	820	mA	<sup>2)</sup>
$I_{DD5B}$	520	550	1100	500	530	1060	mA	<sup>2)</sup>
$I_{DD5D}$	40	70	140	40	70	140	mA	<sup>3)6)</sup>
$I_{DD6}$	20	40	80	20	40	80	mA	<sup>3)6)</sup>
$I_{DD7}$	920	950	1220	880	910	1180	mA	<sup>2)</sup>

1) Calculated values from component data. ODT disabled.  $I_{DD1}$ ,  $I_{DD4R}$ , and  $I_{DD7}$ , are defined with the outputs disabled.

2) The other rank is in  $I_{DD2P}$  Precharge Power-Down Current mode.

3) Both ranks are in the same  $I_{DD}$  current mode.

4) Fast: MRS(12)=0

5) Slow: MRS(12)=1

6)  $I_{DD5D}$  and  $I_{DD6}$  values are for  $0^{\circ}\text{C} \leq T_{\text{Case}} \leq 85^{\circ}\text{C}$

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

## 4 SPD Codes

This chapter lists all hexadecimal byte values stored in the EEPROM of the products described in this data sheet. SPD stands for serial presence detect. All values with XX in the table are module specific bytes which are defined during production.

### List of SPD Code Tables

- [Table 23 “HYS64T\[32/64/128\]0xxHDL-25F-B” on Page 30](#)
- [Table 24 “HYS64T\[32/64/128\]0xxHDL-2.5-B” on Page 35](#)
- [Table 25 “HYS64T\[32/64/128\]0xxHDL-3-B” on Page 39](#)
- [Table 26 “HYS64T\[32/64/128\]0xxHDL-3S-B” on Page 43](#)
- [Table 27 “HYS64T\[32/64/128\]9xxHDL-3S-B” on Page 47](#)
- [Table 28 “HYS64T\[32/64/128\]0xxHDL-3.7-B” on Page 51](#)
- [Table 29 “HYS64T\[32/64/128\]9xxHDL-3.7-B” on Page 55](#)
- [Table 30 “HYS64T\[32/64/128\]0xxHDL-5-B” on Page 59](#)

**TABLE 23**  
**HYS64T[32/64/128]0xxHDL-25F-B**

Product Type	HYS64T32000HDL-25F-B	HYS64T64020HDL-25F-B	HYS64T128021HDL-25F-B
Organization	<b>256MB</b> ×64 <b>1 Rank (×16)</b>	<b>512MB</b> ×64 <b>2 Ranks (×16)</b>	<b>1 GByte</b> ×64 <b>2 Ranks (×8)</b>
Label Code	<b>PC2-6400S-555</b>	<b>PC2-6400S-555</b>	<b>PC2-6400S-555</b>
JEDEC SPD Revision	<b>Rev. 1.2</b>	<b>Rev. 1.2</b>	<b>Rev. 1.2</b>
Byte#	Description	HEX	HEX
0	Programmed SPD Bytes in EEPROM	80	80
1	Total number of Bytes in EEPROM	08	08
2	Memory Type (DDR2)	08	08
3	Number of Row Addresses	0D	0D
4	Number of Column Addresses	0A	0A
5	DIMM Rank and Stacking Information	60	61
6	Data Width	40	40
7	Not used	00	00
8	Interface Voltage Level	05	05

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-25F-B	HYS64T64020HDL-25F-B	HYS64T128021HDL-25F-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-6400S-555	PC2-6400S-555	PC2-6400S-555
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
9	$t_{CK}$ @ CL <sub>MAX</sub> (Byte 18) [ns]	25	25	25
10	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> (Byte 18) [ns]	40	40	40
11	Error Correction Support (non-ECC, ECC)	00	00	00
12	Refresh Rate and Type	82	82	82
13	Primary SDRAM Width	10	10	08
14	Error Checking SDRAM Width	00	00	00
15	Not used	00	00	00
16	Burst Length Supported	0C	0C	0C
17	Number of Banks on SDRAM Device	04	04	04
18	Supported CAS Latencies	70	70	70
19	DIMM Mechanical Characteristics	01	01	01
20	DIMM Type Information	04	04	04
21	DIMM Attributes	00	00	00
22	Component Attributes	07	07	07
23	$t_{CK}$ @ CL <sub>MAX</sub> -1 (Byte 18) [ns]	25	25	25
24	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> -1 [ns]	40	40	40
25	$t_{CK}$ @ CL <sub>MAX</sub> -2 (Byte 18) [ns]	3D	3D	3D
26	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> -2 [ns]	50	50	50
27	$t_{RP,MIN}$ [ns]	32	32	32
28	$t_{RRD,MIN}$ [ns]	28	28	1E
29	$t_{RCD,MIN}$ [ns]	32	32	32
30	$t_{RAS,MIN}$ [ns]	2D	2D	2D
31	Module Density per Rank	40	40	80
32	$t_{AS,MIN}$ and $t_{CS,MIN}$ [ns]	17	17	17
33	$t_{AH,MIN}$ and $t_{CH,MIN}$ [ns]	25	25	25
34	$t_{DS,MIN}$ [ns]	05	05	05

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-25F-B	HYS64T64020HDL-25F-B	HYS64T128021HDL-25F-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-6400S-555	PC2-6400S-555	PC2-6400S-555
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
35	$t_{DH,MIN}$ [ns]	12	12	12
36	$t_{WR,MIN}$ [ns]	3C	3C	3C
37	$t_{WTR,MIN}$ [ns]	1E	1E	1E
38	$t_{RTP,MIN}$ [ns]	1E	1E	1E
39	Analysis Characteristics	00	00	00
40	$t_{RC}$ and $t_{RFC}$ Extension	30	30	30
41	$t_{RC,MIN}$ [ns]	39	39	39
42	$t_{RFC,MIN}$ [ns]	69	69	69
43	$t_{CK,MAX}$ [ns]	80	80	80
44	$t_{DQSQ,MAX}$ [ns]	14	14	14
45	$t_{QHS,MAX}$ [ns]	1E	1E	1E
46	PLL Relock Time	00	00	00
47	$T_{CASE,MAX}$ Delta / $\Delta T_{4R4W}$ Delta	56	56	50
48	Psi(T-A) DRAM	7A	7A	7A
49	$\Delta T_0$ (DT0)	7F	7F	5F
50	$\Delta T_{2N}$ (DT2N, UDIMM) or $\Delta T_{2Q}$ (DT2Q, RDIMM)	3B	3B	3B
51	$\Delta T_{2P}$ (DT2P)	36	36	36
52	$\Delta T_{3N}$ (DT3N)	2E	2E	2E
53	$\Delta T_{3P,fast}$ (DT3P fast)	5A	5A	5A
54	$\Delta T_{3P,slow}$ (DT3P slow)	2A	2A	2A
55	$\Delta T_{4R}$ (DT4R) / $\Delta T_{4R4W}$ Sign (DT4R4W)	68	68	5A
56	$\Delta T_{5B}$ (DT5B)	22	22	22
57	$\Delta T_7$ (DT7)	3D	3D	27
58	Psi(ca) PLL	00	00	00
59	Psi(ca) REG	00	00	00
60	$\Delta T_{PLL}$ (DTPLL)	00	00	00

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-25F-B	HYS64T64020HDL-25F-B	HYS64T128021HDL-25F-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-6400S-555	PC2-6400S-555	PC2-6400S-555
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
61	ΔT <sub>REG</sub> (DTREG) / Toggle Rate	00	00	00
62	SPD Revision	12	12	12
63	Checksum of Bytes 0-62	54	55	3A
64	Manufacturer's JEDEC ID Code (1)	7F	7F	7F
65	Manufacturer's JEDEC ID Code (2)	7F	7F	7F
66	Manufacturer's JEDEC ID Code (3)	7F	7F	7F
67	Manufacturer's JEDEC ID Code (4)	7F	7F	7F
68	Manufacturer's JEDEC ID Code (5)	7F	7F	7F
69	Manufacturer's JEDEC ID Code (6)	51	51	51
70	Manufacturer's JEDEC ID Code (7)	00	00	00
71	Manufacturer's JEDEC ID Code (8)	00	00	00
72	Module Manufacturer Location	xx	xx	xx
73	Product Type, Char 1	36	36	36
74	Product Type, Char 2	34	34	34
75	Product Type, Char 3	54	54	54
76	Product Type, Char 4	33	36	31
77	Product Type, Char 5	32	34	32
78	Product Type, Char 6	30	30	38
79	Product Type, Char 7	30	32	30
80	Product Type, Char 8	30	30	32
81	Product Type, Char 9	48	48	31
82	Product Type, Char 10	44	44	48
83	Product Type, Char 11	4C	4C	44
84	Product Type, Char 12	32	32	4C
85	Product Type, Char 13	35	35	32
86	Product Type, Char 14	46	46	35



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

<b>Product Type</b>		<b>HYS64T32000HDL-25F-B</b>	<b>HYS64T64020HDL-25F-B</b>	<b>HYS64T128021HDL-25F-B</b>
<b>Organization</b>		<b>256MB</b>	<b>512MB</b>	<b>1 GByte</b>
		<b>×64</b>	<b>×64</b>	<b>×64</b>
		<b>1 Rank (×16)</b>	<b>2 Ranks (×16)</b>	<b>2 Ranks (×8)</b>
<b>Label Code</b>		<b>PC2-6400S-555</b>	<b>PC2-6400S-555</b>	<b>PC2-6400S-555</b>
<b>JEDEC SPD Revision</b>		<b>Rev. 1.2</b>	<b>Rev. 1.2</b>	<b>Rev. 1.2</b>
<b>Byte#</b>	<b>Description</b>	<b>HEX</b>	<b>HEX</b>	<b>HEX</b>
87	Product Type, Char 15	42	42	46
88	Product Type, Char 16	20	20	42
89	Product Type, Char 17	20	20	20
90	Product Type, Char 18	20	20	20
91	Module Revision Code	3x	3x	3x
92	Test Program Revision Code	xx	xx	xx
93	Module Manufacturing Date Year	xx	xx	xx
94	Module Manufacturing Date Week	xx	xx	xx
95 - 98	Module Serial Number	xx	xx	xx
99 - 127	Not used	00	00	00
128 - 255	Blank for customer use	FF	FF	FF



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

**TABLE 24**  
**HYS64T[32/64/128]0xxHDL-2.5-B**

Product Type		HYS64T32000HDL-2.5-B	HYS64T64020HDL-2.5-B	HYS64T128021HDL-2.5-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code	PC2-6400S-666	PC2-6400S-666	PC2-6400S-666	
JEDEC SPD Revision	Rev. 1.2	Rev. 1.2	Rev. 1.2	
Byte#	Description	HEX	HEX	HEX
0	Programmed SPD Bytes in EEPROM	80	80	80
1	Total number of Bytes in EEPROM	08	08	08
2	Memory Type (DDR2)	08	08	08
3	Number of Row Addresses	0D	0D	0E
4	Number of Column Addresses	0A	0A	0A
5	DIMM Rank and Stacking Information	60	61	61
6	Data Width	40	40	40
7	Not used	00	00	00
8	Interface Voltage Level	05	05	05
9	$t_{CK}$ @ CL <sub>MAX</sub> (Byte 18) [ns]	25	25	25
10	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> (Byte 18) [ns]	40	40	40
11	Error Correction Support (non-ECC, ECC)	00	00	00
12	Refresh Rate and Type	82	82	82
13	Primary SDRAM Width	10	10	08
14	Error Checking SDRAM Width	00	00	00
15	Not used	00	00	00
16	Burst Length Supported	0C	0C	0C
17	Number of Banks on SDRAM Device	04	04	04
18	Supported CAS Latencies	70	70	70
19	DIMM Mechanical Characteristics	01	01	01
20	DIMM Type Information	04	04	04
21	DIMM Attributes	00	00	00
22	Component Attributes	07	07	07

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-2.5-B	HYS64T64020HDL-2.5-B	HYS64T128021HDL-2.5-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-6400S-666	PC2-6400S-666	PC2-6400S-666
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
23	$t_{CK}$ @ CL <sub>MAX</sub> -1 (Byte 18) [ns]	30	30	30
24	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> -1 [ns]	45	45	45
25	$t_{CK}$ @ CL <sub>MAX</sub> -2 (Byte 18) [ns]	3D	3D	3D
26	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> -2 [ns]	50	50	50
27	$t_{RP,MIN}$ [ns]	3C	3C	3C
28	$t_{RRD,MIN}$ [ns]	28	28	1E
29	$t_{RCD,MIN}$ [ns]	3C	3C	3C
30	$t_{RAS,MIN}$ [ns]	2D	2D	2D
31	Module Density per Rank	40	40	80
32	$t_{AS,MIN}$ and $t_{CS,MIN}$ [ns]	17	17	17
33	$t_{AH,MIN}$ and $t_{CH,MIN}$ [ns]	25	25	25
34	$t_{DS,MIN}$ [ns]	05	05	05
35	$t_{DH,MIN}$ [ns]	12	12	12
36	$t_{WR,MIN}$ [ns]	3C	3C	3C
37	$t_{WTR,MIN}$ [ns]	1E	1E	1E
38	$t_{RTP,MIN}$ [ns]	1E	1E	1E
39	Analysis Characteristics	00	00	00
40	$t_{RC}$ and $t_{RFC}$ Extension	00	00	00
41	$t_{RC,MIN}$ [ns]	3C	3C	3C
42	$t_{RFC,MIN}$ [ns]	69	69	69
43	$t_{CK,MAX}$ [ns]	80	80	80
44	$t_{DQSQ,MAX}$ [ns]	14	14	14
45	$t_{QHS,MAX}$ [ns]	1E	1E	1E
46	PLL Relock Time	00	00	00
47	$T_{CASE,MAX}$ Delta / $\Delta T_{4R4W}$ Delta	55	55	50
48	Psi(T-A) DRAM	72	72	7A

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-2.5-B	HYS64T64020HDL-2.5-B	HYS64T128021HDL-2.5-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-6400S-666	PC2-6400S-666	PC2-6400S-666
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
49	ΔT <sub>0</sub> (DT0)	6F	6F	5B
50	ΔT <sub>2N</sub> (DT2N, UDIMM) or ΔT <sub>2Q</sub> (DT2Q, RDIMM)	37	37	3B
51	ΔT <sub>2P</sub> (DT2P)	33	33	36
52	ΔT <sub>3N</sub> (DT3N)	2B	2B	2E
53	ΔT <sub>3P.fast</sub> (DT3P fast)	54	54	5A
54	ΔT <sub>3P.slow</sub> (DT3P slow)	27	27	2A
55	ΔT <sub>4R</sub> (DT4R) / ΔT <sub>4R4W</sub> Sign (DT4R4W)	62	62	5A
56	ΔT <sub>5B</sub> (DT5B)	1F	1F	22
57	ΔT <sub>7</sub> (DT7)	37	37	25
58	Psi(ca) PLL	00	00	00
59	Psi(ca) REG	00	00	00
60	ΔT <sub>PLL</sub> (DTPLL)	00	00	00
61	ΔT <sub>REG</sub> (DTREG) / Toggle Rate	00	00	00
62	SPD Revision	12	12	12
63	Checksum of Bytes 0-62	10	11	2B
64	Manufacturer's JEDEC ID Code (1)	7F	7F	7F
65	Manufacturer's JEDEC ID Code (2)	7F	7F	7F
66	Manufacturer's JEDEC ID Code (3)	7F	7F	7F
67	Manufacturer's JEDEC ID Code (4)	7F	7F	7F
68	Manufacturer's JEDEC ID Code (5)	7F	7F	7F
69	Manufacturer's JEDEC ID Code (6)	51	51	51
70	Manufacturer's JEDEC ID Code (7)	00	00	00
71	Manufacturer's JEDEC ID Code (8)	00	00	00
72	Module Manufacturer Location	xx	xx	xx
73	Product Type, Char 1	36	36	36
74	Product Type, Char 2	34	34	34

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

<b>Product Type</b>		HYS64T32000HDL-2.5-B	HYS64T64020HDL-2.5-B	HYS64T128021HDL-2.5-B
<b>Organization</b>	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
<b>Label Code</b>		PC2-6400S-666	PC2-6400S-666	PC2-6400S-666
<b>JEDEC SPD Revision</b>		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
75	Product Type, Char 3	54	54	54
76	Product Type, Char 4	33	36	31
77	Product Type, Char 5	32	34	32
78	Product Type, Char 6	30	30	38
79	Product Type, Char 7	30	32	30
80	Product Type, Char 8	30	30	32
81	Product Type, Char 9	48	48	31
82	Product Type, Char 10	44	44	48
83	Product Type, Char 11	4C	4C	44
84	Product Type, Char 12	32	32	4C
85	Product Type, Char 13	2E	2E	32
86	Product Type, Char 14	35	35	2E
87	Product Type, Char 15	42	42	35
88	Product Type, Char 16	20	20	42
89	Product Type, Char 17	20	20	20
90	Product Type, Char 18	20	20	20
91	Module Revision Code	4x	4x	4x
92	Test Program Revision Code	xx	xx	xx
93	Module Manufacturing Date Year	xx	xx	xx
94	Module Manufacturing Date Week	xx	xx	xx
95 - 98	Module Serial Number	xx	xx	xx
99 - 127	Not used	00	00	00
128 - 255	Blank for customer use	FF	FF	FF



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

**TABLE 25**  
**HYS64T[32/64/128]0xxHDL-3-B**

Product Type		HYS64T32000HDL-3-B	HYS64T64020HDL-3-B	HYS64T128021HDL-3-B
Organization	<b>256MB</b>	<b>512MB</b>	<b>1 GByte</b>	
	<b>×64</b>	<b>×64</b>	<b>×64</b>	
	<b>1 Rank (×16)</b>	<b>2 Ranks (×16)</b>	<b>2 Ranks (×8)</b>	
Label Code		PC2-5300S-444	PC2-5300S-444	PC2-5300S-444
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
0	Programmed SPD Bytes in EEPROM	80	80	80
1	Total number of Bytes in EEPROM	08	08	08
2	Memory Type (DDR2)	08	08	08
3	Number of Row Addresses	0D	0D	0E
4	Number of Column Addresses	0A	0A	0A
5	DIMM Rank and Stacking Information	60	61	61
6	Data Width	40	40	40
7	Not used	00	00	00
8	Interface Voltage Level	05	05	05
9	$t_{CK}$ @ CL <sub>MAX</sub> (Byte 18) [ns]	30	30	30
10	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> (Byte 18) [ns]	45	45	45
11	Error Correction Support (non-ECC, ECC)	00	00	00
12	Refresh Rate and Type	82	82	82
13	Primary SDRAM Width	10	10	08
14	Error Checking SDRAM Width	00	00	00
15	Not used	00	00	00
16	Burst Length Supported	0C	0C	0C
17	Number of Banks on SDRAM Device	04	04	04
18	Supported CAS Latencies	38	38	38
19	DIMM Mechanical Characteristics	01	01	01
20	DIMM Type Information	04	04	04
21	DIMM Attributes	00	00	00
22	Component Attributes	07	07	07
23	$t_{CK}$ @ CL <sub>MAX</sub> -1 (Byte 18) [ns]	30	30	30

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-3-B	HYS64T64020HDL-3-B	HYS64T128021HDL-3-B
Organization	<b>256MB</b>	<b>512MB</b>	<b>1 GByte</b>	
	<b>×64</b>	<b>×64</b>	<b>×64</b>	
	<b>1 Rank (×16)</b>	<b>2 Ranks (×16)</b>	<b>2 Ranks (×8)</b>	
Label Code		PC2-5300S-444	PC2-5300S-444	PC2-5300S-444
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
24	$t_{AC}$ SDRAM @ $CL_{MAX}$ -1 [ns]	45	45	45
25	$t_{CK}$ @ $CL_{MAX}$ -2 (Byte 18) [ns]	50	50	50
26	$t_{AC}$ SDRAM @ $CL_{MAX}$ -2 [ns]	60	60	60
27	$t_{RP,MIN}$ [ns]	30	30	30
28	$t_{RRD,MIN}$ [ns]	28	28	1E
29	$t_{RCD,MIN}$ [ns]	30	30	30
30	$t_{RAS,MIN}$ [ns]	2D	2D	2D
31	Module Density per Rank	40	40	80
32	$t_{AS,MIN}$ and $t_{CS,MIN}$ [ns]	20	20	20
33	$t_{AH,MIN}$ and $t_{CH,MIN}$ [ns]	27	27	27
34	$t_{DS,MIN}$ [ns]	10	10	10
35	$t_{DH,MIN}$ [ns]	17	17	17
36	$t_{WR,MIN}$ [ns]	3C	3C	3C
37	$t_{WTR,MIN}$ [ns]	1E	1E	1E
38	$t_{RTP,MIN}$ [ns]	1E	1E	1E
39	Analysis Characteristics	00	00	00
40	$t_{RC}$ and $t_{RFC}$ Extension	00	00	00
41	$t_{RC,MIN}$ [ns]	39	39	39
42	$t_{RFC,MIN}$ [ns]	69	69	69
43	$t_{CK,MAX}$ [ns]	80	80	80
44	$t_{DQSQ,MAX}$ [ns]	18	18	18
45	$t_{QHS,MAX}$ [ns]	22	22	22
46	PLL Relock Time	00	00	00
47	$T_{CASE,MAX}$ Delta / $\Delta T_{4R4W}$ Delta	54	54	50
48	Psi(T-A) DRAM	72	72	7A
49	$\Delta T_0$ (DT0)	67	67	53

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-3-B	HYS64T64020HDL-3-B	HYS64T128021HDL-3-B
Organization	<b>256MB</b>	<b>512MB</b>	<b>1 GByte</b>	
	<b>x64</b>	<b>x64</b>	<b>x64</b>	
	<b>1 Rank (x16)</b>	<b>2 Ranks (x16)</b>	<b>2 Ranks (x8)</b>	
Label Code		PC2-5300S-444	PC2-5300S-444	PC2-5300S-444
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
50	$\Delta T_{2N}$ (DT2N, UDIMM) or $\Delta T_{2Q}$ (DT2Q, RDIMM)	31	31	34
51	$\Delta T_{2P}$ (DT2P)	33	33	36
52	$\Delta T_{3N}$ (DT3N)	24	24	27
53	$\Delta T_{3P,fast}$ (DT3P fast)	47	47	4C
54	$\Delta T_{3P,slow}$ (DT3P slow)	27	27	2A
55	$\Delta T_{4R}$ (DT4R) / $\Delta T_{4R4W}$ Sign (DT4R4W)	54	54	4C
56	$\Delta T_{5B}$ (DT5B)	1E	1E	20
57	$\Delta T_7$ (DT7)	37	37	25
58	Psi(ca) PLL	00	00	00
59	Psi(ca) REG	00	00	00
60	$\Delta T_{PLL}$ (DTPLL)	00	00	00
61	$\Delta T_{REG}$ (DTREG) / Toggle Rate	00	00	00
62	SPD Revision	12	12	12
63	Checksum of Bytes 0-62	E1	E2	FA
64	Manufacturer's JEDEC ID Code (1)	7F	7F	7F
65	Manufacturer's JEDEC ID Code (2)	7F	7F	7F
66	Manufacturer's JEDEC ID Code (3)	7F	7F	7F
67	Manufacturer's JEDEC ID Code (4)	7F	7F	7F
68	Manufacturer's JEDEC ID Code (5)	7F	7F	7F
69	Manufacturer's JEDEC ID Code (6)	51	51	51
70	Manufacturer's JEDEC ID Code (7)	00	00	00
71	Manufacturer's JEDEC ID Code (8)	00	00	00
72	Module Manufacturer Location	xx	xx	xx
73	Product Type, Char 1	36	36	36
74	Product Type, Char 2	34	34	34
75	Product Type, Char 3	54	54	54

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-3-B	HYS64T64020HDL-3-B	HYS64T128021HDL-3-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-5300S-444	PC2-5300S-444	PC2-5300S-444
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
76	Product Type, Char 4	33	36	31
77	Product Type, Char 5	32	34	32
78	Product Type, Char 6	30	30	38
79	Product Type, Char 7	30	32	30
80	Product Type, Char 8	30	30	32
81	Product Type, Char 9	48	48	31
82	Product Type, Char 10	44	44	48
83	Product Type, Char 11	4C	4C	44
84	Product Type, Char 12	33	33	4C
85	Product Type, Char 13	42	42	33
86	Product Type, Char 14	20	20	42
87	Product Type, Char 15	20	20	20
88	Product Type, Char 16	20	20	20
89	Product Type, Char 17	20	20	20
90	Product Type, Char 18	20	20	20
91	Module Revision Code	3x	3x	4x
92	Test Program Revision Code	xx	xx	xx
93	Module Manufacturing Date Year	xx	xx	xx
94	Module Manufacturing Date Week	xx	xx	xx
95 - 98	Module Serial Number	xx	xx	xx
99 - 127	Not used	00	00	00
128 - 255	Blank for customer use	FF	FF	FF

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module**TABLE 26**  
**HYS64T[32/64/128]0xxHDL-3S-B**

Product Type	HYS64T32000HDL-3S-B	HYS64T64020HDL-3S-B	HYS64T128021HDL-3S-B
Organization	<b>256MB</b> ×64 <b>1 Rank (×16)</b>	<b>512MB</b> ×64 <b>2 Ranks (×16)</b>	<b>1 GByte</b> ×64 <b>2 Ranks (×8)</b>
Label Code	<b>PC2-5300S-555</b>	<b>PC2-5300S-555</b>	<b>PC2-5300S-555</b>
JEDEC SPD Revision	<b>Rev. 1.2</b>	<b>Rev. 1.2</b>	<b>Rev. 1.2</b>
Byte#	Description	HEX	HEX
0	Programmed SPD Bytes in EEPROM	80	80
1	Total number of Bytes in EEPROM	08	08
2	Memory Type (DDR2)	08	08
3	Number of Row Addresses	0D	0D
4	Number of Column Addresses	0A	0A
5	DIMM Rank and Stacking Information	60	61
6	Data Width	40	40
7	Not used	00	00
8	Interface Voltage Level	05	05
9	$t_{CK}$ @ CL <sub>MAX</sub> (Byte 18) [ns]	30	30
10	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> (Byte 18) [ns]	45	45
11	Error Correction Support (non-ECC, ECC)	00	00
12	Refresh Rate and Type	82	82
13	Primary SDRAM Width	10	10
14	Error Checking SDRAM Width	00	00
15	Not used	00	00
16	Burst Length Supported	0C	0C
17	Number of Banks on SDRAM Device	04	04
18	Supported CAS Latencies	38	38
19	DIMM Mechanical Characteristics	01	01
20	DIMM Type Information	04	04
21	DIMM Attributes	00	00
22	Component Attributes	07	07

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-3S-B	HYS64T64020HDL-3S-B	HYS64T128021HDL-3S-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-5300S-555	PC2-5300S-555	PC2-5300S-555
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
23	$t_{CK}$ @ CL <sub>MAX</sub> -1 (Byte 18) [ns]	3D	3D	3D
24	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> -1 [ns]	50	50	50
25	$t_{CK}$ @ CL <sub>MAX</sub> -2 (Byte 18) [ns]	50	50	50
26	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> -2 [ns]	60	60	60
27	$t_{RP,MIN}$ [ns]	3C	3C	3C
28	$t_{RRD,MIN}$ [ns]	28	28	1E
29	$t_{RCD,MIN}$ [ns]	3C	3C	3C
30	$t_{RAS,MIN}$ [ns]	2D	2D	2D
31	Module Density per Rank	40	40	80
32	$t_{AS,MIN}$ and $t_{CS,MIN}$ [ns]	20	20	20
33	$t_{AH,MIN}$ and $t_{CH,MIN}$ [ns]	27	27	27
34	$t_{DS,MIN}$ [ns]	10	10	10
35	$t_{DH,MIN}$ [ns]	17	17	17
36	$t_{WR,MIN}$ [ns]	3C	3C	3C
37	$t_{WTR,MIN}$ [ns]	1E	1E	1E
38	$t_{RTP,MIN}$ [ns]	1E	1E	1E
39	Analysis Characteristics	00	00	00
40	$t_{RC}$ and $t_{RFC}$ Extension	00	00	00
41	$t_{RC,MIN}$ [ns]	3C	3C	3C
42	$t_{RFC,MIN}$ [ns]	69	69	69
43	$t_{CK,MAX}$ [ns]	80	80	80
44	$t_{DQSQ,MAX}$ [ns]	18	18	18
45	$t_{QHS,MAX}$ [ns]	22	22	22
46	PLL Relock Time	00	00	00
47	$T_{CASE,MAX}$ Delta / $\Delta T_{4R4W}$ Delta	54	54	50
48	Psi(T-A) DRAM	72	72	7A

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-3S-B	HYS64T64020HDL-3S-B	HYS64T128021HDL-3S-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-5300S-555	PC2-5300S-555	PC2-5300S-555
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
49	ΔT <sub>0</sub> (DT0)	5F	5F	4B
50	ΔT <sub>2N</sub> (DT2N, UDIMM) or ΔT <sub>2Q</sub> (DT2Q, RDIMM)	31	31	34
51	ΔT <sub>2P</sub> (DT2P)	33	33	36
52	ΔT <sub>3N</sub> (DT3N)	24	24	27
53	ΔT <sub>3P.fast</sub> (DT3P fast)	47	47	4C
54	ΔT <sub>3P.slow</sub> (DT3P slow)	27	27	2A
55	ΔT <sub>4R</sub> (DT4R) / ΔT <sub>4R4W</sub> Sign (DT4R4W)	54	54	4C
56	ΔT <sub>5B</sub> (DT5B)	1E	1E	20
57	ΔT <sub>7</sub> (DT7)	34	34	23
58	Psi(ca) PLL	00	00	00
59	Psi(ca) REG	00	00	00
60	ΔT <sub>PLL</sub> (DTPLL)	00	00	00
61	ΔT <sub>REG</sub> (DTREG) / Toggle Rate	00	00	00
62	SPD Revision	12	12	12
63	Checksum of Bytes 0-62	09	0A	23
64	Manufacturer's JEDEC ID Code (1)	7F	7F	7F
65	Manufacturer's JEDEC ID Code (2)	7F	7F	7F
66	Manufacturer's JEDEC ID Code (3)	7F	7F	7F
67	Manufacturer's JEDEC ID Code (4)	7F	7F	7F
68	Manufacturer's JEDEC ID Code (5)	7F	7F	7F
69	Manufacturer's JEDEC ID Code (6)	51	51	51
70	Manufacturer's JEDEC ID Code (7)	00	00	00
71	Manufacturer's JEDEC ID Code (8)	00	00	00
72	Module Manufacturer Location	xx	xx	xx
73	Product Type, Char 1	36	36	36
74	Product Type, Char 2	34	34	34

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-3S-B	HYS64T64020HDL-3S-B	HYS64T128021HDL-3S-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-5300S-555	PC2-5300S-555	PC2-5300S-555
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
75	Product Type, Char 3	54	54	54
76	Product Type, Char 4	33	36	31
77	Product Type, Char 5	32	34	32
78	Product Type, Char 6	30	30	38
79	Product Type, Char 7	30	32	30
80	Product Type, Char 8	30	30	32
81	Product Type, Char 9	48	48	31
82	Product Type, Char 10	44	44	48
83	Product Type, Char 11	4C	4C	44
84	Product Type, Char 12	33	33	4C
85	Product Type, Char 13	53	53	33
86	Product Type, Char 14	42	42	53
87	Product Type, Char 15	20	20	42
88	Product Type, Char 16	20	20	20
89	Product Type, Char 17	20	20	20
90	Product Type, Char 18	20	20	20
91	Module Revision Code	4x	4x	4x
92	Test Program Revision Code	xx	xx	xx
93	Module Manufacturing Date Year	xx	xx	xx
94	Module Manufacturing Date Week	xx	xx	xx
95 - 98	Module Serial Number	xx	xx	xx
99 - 127	Not used	00	00	00
128 - 255	Blank for customer use	FF	FF	FF

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module**TABLE 27**  
**HYS64T[32/64/128]9xxHDL-3S-B**

Product Type	HYS64T32900HDL-3S-B	HYS64T64920HDL-3S-B	HYS64T128921HDL-3S-B
Organization	<b>256MB</b> x64 <b>1 Rank (x16)</b>	<b>512MB</b> x64 <b>2 Ranks (x16)</b>	<b>1 GByte</b> x64 <b>2 Ranks (x8)</b>
Label Code	<b>PC2-5300S-555</b>	<b>PC2-5300S-555</b>	<b>PC2-5300S-555</b>
JEDEC SPD Revision	<b>Rev. 1.2</b>	<b>Rev. 1.2</b>	<b>Rev. 1.2</b>
Byte#	Description	HEX	HEX
0	Programmed SPD Bytes in EEPROM	80	80
1	Total number of Bytes in EEPROM	08	08
2	Memory Type (DDR2)	08	08
3	Number of Row Addresses	0D	0D
4	Number of Column Addresses	0A	0A
5	DIMM Rank and Stacking Information	60	61
6	Data Width	40	40
7	Not used	00	00
8	Interface Voltage Level	05	05
9	$t_{CK}$ @ CL <sub>MAX</sub> (Byte 18) [ns]	30	30
10	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> (Byte 18) [ns]	45	45
11	Error Correction Support (non-ECC, ECC)	00	00
12	Refresh Rate and Type	82	82
13	Primary SDRAM Width	10	10
14	Error Checking SDRAM Width	00	00
15	Not used	00	00
16	Burst Length Supported	0C	0C
17	Number of Banks on SDRAM Device	04	04
18	Supported CAS Latencies	38	38
19	DIMM Mechanical Characteristics	01	01
20	DIMM Type Information	04	04
21	DIMM Attributes	00	00
22	Component Attributes	07	07

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32900HDL-3S-B	HYS64T64920HDL-3S-B	HYS64T128921HDL-3S-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-5300S-555	PC2-5300S-555	PC2-5300S-555
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
23	$t_{CK}$ @ CL <sub>MAX</sub> -1 (Byte 18) [ns]	3D	3D	3D
24	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> -1 [ns]	50	50	50
25	$t_{CK}$ @ CL <sub>MAX</sub> -2 (Byte 18) [ns]	50	50	50
26	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> -2 [ns]	60	60	60
27	$t_{RP,MIN}$ [ns]	3C	3C	3C
28	$t_{RRD,MIN}$ [ns]	28	28	1E
29	$t_{RCD,MIN}$ [ns]	3C	3C	3C
30	$t_{RAS,MIN}$ [ns]	2D	2D	2D
31	Module Density per Rank	40	40	80
32	$t_{AS,MIN}$ and $t_{CS,MIN}$ [ns]	20	20	20
33	$t_{AH,MIN}$ and $t_{CH,MIN}$ [ns]	27	27	27
34	$t_{DS,MIN}$ [ns]	10	10	10
35	$t_{DH,MIN}$ [ns]	17	17	17
36	$t_{WR,MIN}$ [ns]	3C	3C	3C
37	$t_{WTR,MIN}$ [ns]	1E	1E	1E
38	$t_{RTP,MIN}$ [ns]	1E	1E	1E
39	Analysis Characteristics	00	00	00
40	$t_{RC}$ and $t_{RFC}$ Extension	00	00	00
41	$t_{RC,MIN}$ [ns]	3C	3C	3C
42	$t_{RFC,MIN}$ [ns]	69	69	69
43	$t_{CK,MAX}$ [ns]	80	80	80
44	$t_{DQSQ,MAX}$ [ns]	18	18	18
45	$t_{QHS,MAX}$ [ns]	22	22	22
46	PLL Relock Time	00	00	00
47	$T_{CASE,MAX}$ Delta / $\Delta T_{4R4W}$ Delta	54	54	50
48	Psi(T-A) DRAM	72	72	7A

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32900HDL-3S-B	HYS64T64920HDL-3S-B	HYS64T128921HDL-3S-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-5300S-555	PC2-5300S-555	PC2-5300S-555
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
49	ΔT <sub>0</sub> (DT0)	5F	5F	4B
50	ΔT <sub>2N</sub> (DT2N, UDIMM) or ΔT <sub>2Q</sub> (DT2Q, RDIMM)	31	31	34
51	ΔT <sub>2P</sub> (DT2P)	33	33	36
52	ΔT <sub>3N</sub> (DT3N)	24	24	27
53	ΔT <sub>3P.fast</sub> (DT3P fast)	47	47	4C
54	ΔT <sub>3P.slow</sub> (DT3P slow)	27	27	2A
55	ΔT <sub>4R</sub> (DT4R) / ΔT <sub>4R4W</sub> Sign (DT4R4W)	54	54	4C
56	ΔT <sub>5B</sub> (DT5B)	1E	1E	20
57	ΔT <sub>7</sub> (DT7)	34	34	23
58	Psi(ca) PLL	00	00	00
59	Psi(ca) REG	00	00	00
60	ΔT <sub>PLL</sub> (DTPLL)	00	00	00
61	ΔT <sub>REG</sub> (DTREG) / Toggle Rate	00	00	00
62	SPD Revision	12	12	12
63	Checksum of Bytes 0-62	09	0A	23
64	Manufacturer's JEDEC ID Code (1)	7F	7F	7F
65	Manufacturer's JEDEC ID Code (2)	7F	7F	7F
66	Manufacturer's JEDEC ID Code (3)	7F	7F	7F
67	Manufacturer's JEDEC ID Code (4)	7F	7F	7F
68	Manufacturer's JEDEC ID Code (5)	7F	7F	7F
69	Manufacturer's JEDEC ID Code (6)	51	51	51
70	Manufacturer's JEDEC ID Code (7)	00	00	00
71	Manufacturer's JEDEC ID Code (8)	00	00	00
72	Module Manufacturer Location	xx	xx	xx
73	Product Type, Char 1	36	36	36
74	Product Type, Char 2	34	34	34

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

<b>Product Type</b>		HYS64T32900HDL-3S-B	HYS64T64920HDL-3S-B	HYS64T128921HDL-3S-B
<b>Organization</b>	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
<b>Label Code</b>		PC2-5300S-555	PC2-5300S-555	PC2-5300S-555
<b>JEDEC SPD Revision</b>		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
75	Product Type, Char 3	54	54	54
76	Product Type, Char 4	33	36	31
77	Product Type, Char 5	32	34	32
78	Product Type, Char 6	39	39	38
79	Product Type, Char 7	30	32	39
80	Product Type, Char 8	30	30	32
81	Product Type, Char 9	48	48	31
82	Product Type, Char 10	44	44	48
83	Product Type, Char 11	4C	4C	44
84	Product Type, Char 12	33	33	4C
85	Product Type, Char 13	53	53	33
86	Product Type, Char 14	42	42	53
87	Product Type, Char 15	20	20	42
88	Product Type, Char 16	20	20	20
89	Product Type, Char 17	20	20	20
90	Product Type, Char 18	20	20	20
91	Module Revision Code	2x	2x	2x
92	Test Program Revision Code	xx	xx	xx
93	Module Manufacturing Date Year	xx	xx	xx
94	Module Manufacturing Date Week	xx	xx	xx
95 - 98	Module Serial Number	xx	xx	xx
99 - 127	Not used	00	00	00
128 - 255	Blank for customer use	FF	FF	FF



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

**TABLE 28**  
**HYS64T[32/64/128]0xxHDL-3.7-B**

Product Type		HYS64T32000HDL-3.7-B	HYS64T64020HDL-3.7-B	HYS64T128021HDL-3.7-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-4200S-444	PC2-4200S-444	PC2-4200S-444
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
0	Programmed SPD Bytes in EEPROM	80	80	80
1	Total number of Bytes in EEPROM	08	08	08
2	Memory Type (DDR2)	08	08	08
3	Number of Row Addresses	0D	0D	0E
4	Number of Column Addresses	0A	0A	0A
5	DIMM Rank and Stacking Information	60	61	61
6	Data Width	40	40	40
7	Not used	00	00	00
8	Interface Voltage Level	05	05	05
9	$t_{CK}$ @ CL <sub>MAX</sub> (Byte 18) [ns]	3D	3D	3D
10	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> (Byte 18) [ns]	50	50	50
11	Error Correction Support (non-ECC, ECC)	00	00	00
12	Refresh Rate and Type	82	82	82
13	Primary SDRAM Width	10	10	08
14	Error Checking SDRAM Width	00	00	00
15	Not used	00	00	00
16	Burst Length Supported	0C	0C	0C
17	Number of Banks on SDRAM Device	04	04	04
18	Supported CAS Latencies	38	38	38
19	DIMM Mechanical Characteristics	01	01	01
20	DIMM Type Information	04	04	04
21	DIMM Attributes	00	00	00
22	Component Attributes	07	07	07

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-3.7-B	HYS64T64020HDL-3.7-B	HYS64T128021HDL-3.7-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-4200S-444	PC2-4200S-444	PC2-4200S-444
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
23	$t_{CK}$ @ CL <sub>MAX</sub> -1 (Byte 18) [ns]	3D	3D	3D
24	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> -1 [ns]	50	50	50
25	$t_{CK}$ @ CL <sub>MAX</sub> -2 (Byte 18) [ns]	50	50	50
26	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> -2 [ns]	60	60	60
27	$t_{RP,MIN}$ [ns]	3C	3C	3C
28	$t_{RRD,MIN}$ [ns]	28	28	1E
29	$t_{RCD,MIN}$ [ns]	3C	3C	3C
30	$t_{RAS,MIN}$ [ns]	2D	2D	2D
31	Module Density per Rank	40	40	80
32	$t_{AS,MIN}$ and $t_{CS,MIN}$ [ns]	25	25	25
33	$t_{AH,MIN}$ and $t_{CH,MIN}$ [ns]	37	37	37
34	$t_{DS,MIN}$ [ns]	10	10	10
35	$t_{DH,MIN}$ [ns]	22	22	22
36	$t_{WR,MIN}$ [ns]	3C	3C	3C
37	$t_{WTR,MIN}$ [ns]	1E	1E	1E
38	$t_{RTP,MIN}$ [ns]	1E	1E	1E
39	Analysis Characteristics	00	00	00
40	$t_{RC}$ and $t_{RFC}$ Extension	00	00	00
41	$t_{RC,MIN}$ [ns]	3C	3C	3C
42	$t_{RFC,MIN}$ [ns]	69	69	69
43	$t_{CK,MAX}$ [ns]	80	80	80
44	$t_{DQSQ,MAX}$ [ns]	1E	1E	1E
45	$t_{QHS,MAX}$ [ns]	28	28	28
46	PLL Relock Time	00	00	00
47	$T_{CASE,MAX}$ Delta / $\Delta T_{4R4W}$ Delta	54	54	50
48	Psi(T-A) DRAM	72	72	7A

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-3.7-B	HYS64T64020HDL-3.7-B	HYS64T128021HDL-3.7-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-4200S-444	PC2-4200S-444	PC2-4200S-444
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
49	ΔT <sub>0</sub> (DT0)	53	53	43
50	ΔT <sub>2N</sub> (DT2N, UDIMM) or ΔT <sub>2Q</sub> (DT2Q, RDIMM)	29	29	2C
51	ΔT <sub>2P</sub> (DT2P)	33	33	36
52	ΔT <sub>3N</sub> (DT3N)	1F	1F	21
53	ΔT <sub>3P.fast</sub> (DT3P fast)	3D	3D	41
54	ΔT <sub>3P.slow</sub> (DT3P slow)	27	27	2A
55	ΔT <sub>4R</sub> (DT4R) / ΔT <sub>4R4W</sub> Sign (DT4R4W)	46	46	40
56	ΔT <sub>5B</sub> (DT5B)	1C	1C	1E
57	ΔT <sub>7</sub> (DT7)	32	32	22
58	Psi(ca) PLL	00	00	00
59	Psi(ca) REG	00	00	00
60	ΔT <sub>PLL</sub> (DTPLL)	00	00	00
61	ΔT <sub>REG</sub> (DTREG) / Toggle Rate	00	00	00
62	SPD Revision	12	12	12
63	Checksum of Bytes 0-62	18	19	37
64	Manufacturer's JEDEC ID Code (1)	7F	7F	7F
65	Manufacturer's JEDEC ID Code (2)	7F	7F	7F
66	Manufacturer's JEDEC ID Code (3)	7F	7F	7F
67	Manufacturer's JEDEC ID Code (4)	7F	7F	7F
68	Manufacturer's JEDEC ID Code (5)	7F	7F	7F
69	Manufacturer's JEDEC ID Code (6)	51	51	51
70	Manufacturer's JEDEC ID Code (7)	00	00	00
71	Manufacturer's JEDEC ID Code (8)	00	00	00
72	Module Manufacturer Location	xx	xx	xx
73	Product Type, Char 1	36	36	36
74	Product Type, Char 2	34	34	34

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-3.7-B	HYS64T64020HDL-3.7-B	HYS64T128021HDL-3.7-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-4200S-444	PC2-4200S-444	PC2-4200S-444
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
75	Product Type, Char 3	54	54	54
76	Product Type, Char 4	33	36	31
77	Product Type, Char 5	32	34	32
78	Product Type, Char 6	30	30	38
79	Product Type, Char 7	30	32	30
80	Product Type, Char 8	30	30	32
81	Product Type, Char 9	48	48	31
82	Product Type, Char 10	44	44	48
83	Product Type, Char 11	4C	4C	44
84	Product Type, Char 12	33	33	4C
85	Product Type, Char 13	2E	2E	33
86	Product Type, Char 14	37	37	2E
87	Product Type, Char 15	42	42	37
88	Product Type, Char 16	20	20	42
89	Product Type, Char 17	20	20	20
90	Product Type, Char 18	20	20	20
91	Module Revision Code	4x	4x	4x
92	Test Program Revision Code	xx	xx	xx
93	Module Manufacturing Date Year	xx	xx	xx
94	Module Manufacturing Date Week	xx	xx	xx
95 - 98	Module Serial Number	xx	xx	xx
99 - 127	Not used	00	00	00
128 - 255	Blank for customer use	FF	FF	FF



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

**TABLE 29**  
**HYS64T[32/64/128]9xxHDL-3.7-B**

Product Type		HYS64T32900HDL-3.7-B	HYS64T64920HDL-3.7-B	HYS64T128921HDL-3.7-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code	PC2-4200S-444	PC2-4200S-444	PC2-4200S-444	
JEDEC SPD Revision	Rev. 1.2	Rev. 1.2	Rev. 1.2	
Byte#	Description	HEX	HEX	HEX
0	Programmed SPD Bytes in EEPROM	80	80	80
1	Total number of Bytes in EEPROM	08	08	08
2	Memory Type (DDR2)	08	08	08
3	Number of Row Addresses	0D	0D	0E
4	Number of Column Addresses	0A	0A	0A
5	DIMM Rank and Stacking Information	60	61	61
6	Data Width	40	40	40
7	Not used	00	00	00
8	Interface Voltage Level	05	05	05
9	$t_{CK}$ @ CL <sub>MAX</sub> (Byte 18) [ns]	3D	3D	3D
10	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> (Byte 18) [ns]	50	50	50
11	Error Correction Support (non-ECC, ECC)	00	00	00
12	Refresh Rate and Type	82	82	82
13	Primary SDRAM Width	10	10	08
14	Error Checking SDRAM Width	00	00	00
15	Not used	00	00	00
16	Burst Length Supported	0C	0C	0C
17	Number of Banks on SDRAM Device	04	04	04
18	Supported CAS Latencies	38	38	38
19	DIMM Mechanical Characteristics	01	01	01
20	DIMM Type Information	04	04	04
21	DIMM Attributes	00	00	00
22	Component Attributes	07	07	07

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32900HDL-3.7-B	HYS64T64920HDL-3.7-B	HYS64T128921HDL-3.7-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-4200S-444	PC2-4200S-444	PC2-4200S-444
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
23	$t_{CK}$ @ CL <sub>MAX</sub> -1 (Byte 18) [ns]	3D	3D	3D
24	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> -1 [ns]	50	50	50
25	$t_{CK}$ @ CL <sub>MAX</sub> -2 (Byte 18) [ns]	50	50	50
26	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> -2 [ns]	60	60	60
27	$t_{RP,MIN}$ [ns]	3C	3C	3C
28	$t_{RRD,MIN}$ [ns]	28	28	1E
29	$t_{RCD,MIN}$ [ns]	3C	3C	3C
30	$t_{RAS,MIN}$ [ns]	2D	2D	2D
31	Module Density per Rank	40	40	80
32	$t_{AS,MIN}$ and $t_{CS,MIN}$ [ns]	25	25	25
33	$t_{AH,MIN}$ and $t_{CH,MIN}$ [ns]	37	37	37
34	$t_{DS,MIN}$ [ns]	10	10	10
35	$t_{DH,MIN}$ [ns]	22	22	22
36	$t_{WR,MIN}$ [ns]	3C	3C	3C
37	$t_{WTR,MIN}$ [ns]	1E	1E	1E
38	$t_{RTP,MIN}$ [ns]	1E	1E	1E
39	Analysis Characteristics	00	00	00
40	$t_{RC}$ and $t_{RFC}$ Extension	00	00	00
41	$t_{RC,MIN}$ [ns]	3C	3C	3C
42	$t_{RFC,MIN}$ [ns]	69	69	69
43	$t_{CK,MAX}$ [ns]	80	80	80
44	$t_{DQSQ,MAX}$ [ns]	1E	1E	1E
45	$t_{QHS,MAX}$ [ns]	28	28	28
46	PLL Relock Time	00	00	00
47	$T_{CASE,MAX}$ Delta / $\Delta T_{4R4W}$ Delta	54	54	50
48	Psi(T-A) DRAM	72	72	7A

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32900HDL-3.7-B	HYS64T64920HDL-3.7-B	HYS64T128921HDL-3.7-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-4200S-444	PC2-4200S-444	PC2-4200S-444
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
49	ΔT <sub>0</sub> (DT0)	53	53	43
50	ΔT <sub>2N</sub> (DT2N, UDIMM) or ΔT <sub>2Q</sub> (DT2Q, RDIMM)	29	29	2C
51	ΔT <sub>2P</sub> (DT2P)	33	33	36
52	ΔT <sub>3N</sub> (DT3N)	1F	1F	21
53	ΔT <sub>3P.fast</sub> (DT3P fast)	3D	3D	41
54	ΔT <sub>3P.slow</sub> (DT3P slow)	27	27	2A
55	ΔT <sub>4R</sub> (DT4R) / ΔT <sub>4R4W</sub> Sign (DT4R4W)	46	46	40
56	ΔT <sub>5B</sub> (DT5B)	1C	1C	1E
57	ΔT <sub>7</sub> (DT7)	32	32	22
58	Psi(ca) PLL	00	00	00
59	Psi(ca) REG	00	00	00
60	ΔT <sub>PLL</sub> (DTPLL)	00	00	00
61	ΔT <sub>REG</sub> (DTREG) / Toggle Rate	00	00	00
62	SPD Revision	12	12	12
63	Checksum of Bytes 0-62	18	19	37
64	Manufacturer's JEDEC ID Code (1)	7F	7F	7F
65	Manufacturer's JEDEC ID Code (2)	7F	7F	7F
66	Manufacturer's JEDEC ID Code (3)	7F	7F	7F
67	Manufacturer's JEDEC ID Code (4)	7F	7F	7F
68	Manufacturer's JEDEC ID Code (5)	7F	7F	7F
69	Manufacturer's JEDEC ID Code (6)	51	51	51
70	Manufacturer's JEDEC ID Code (7)	00	00	00
71	Manufacturer's JEDEC ID Code (8)	00	00	00
72	Module Manufacturer Location	xx	xx	xx
73	Product Type, Char 1	36	36	36
74	Product Type, Char 2	34	34	34

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

<b>Product Type</b>		HYS64T32900HDL-3.7-B	HYS64T64920HDL-3.7-B	HYS64T128921HDL-3.7-B
<b>Organization</b>	<b>256MB</b>	<b>512MB</b>	<b>1 GByte</b>	
	<b>×64</b>	<b>×64</b>	<b>×64</b>	
	<b>1 Rank (×16)</b>	<b>2 Ranks (×16)</b>	<b>2 Ranks (×8)</b>	
<b>Label Code</b>		PC2-4200S-444	PC2-4200S-444	PC2-4200S-444
<b>JEDEC SPD Revision</b>		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
75	Product Type, Char 3	54	54	54
76	Product Type, Char 4	33	36	31
77	Product Type, Char 5	32	34	32
78	Product Type, Char 6	39	39	38
79	Product Type, Char 7	30	32	39
80	Product Type, Char 8	30	30	32
81	Product Type, Char 9	48	48	31
82	Product Type, Char 10	44	44	48
83	Product Type, Char 11	4C	4C	44
84	Product Type, Char 12	33	33	4C
85	Product Type, Char 13	2E	2E	33
86	Product Type, Char 14	37	37	2E
87	Product Type, Char 15	42	42	37
88	Product Type, Char 16	20	20	42
89	Product Type, Char 17	20	20	20
90	Product Type, Char 18	20	20	20
91	Module Revision Code	2x	2x	2x
92	Test Program Revision Code	xx	xx	xx
93	Module Manufacturing Date Year	xx	xx	xx
94	Module Manufacturing Date Week	xx	xx	xx
95 - 98	Module Serial Number	xx	xx	xx
99 - 127	Not used	00	00	00
128 - 255	Blank for customer use	FF	FF	FF

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module**TABLE 30**  
**HYS64T[32/64/128]0xxHDL-5-B**

Product Type		HYS64T32000HDL-5-B	HYS64T64020HDL-5-B	HYS64T128021HDL-5-B
Organization	<b>256MB</b>	<b>512MB</b>	<b>1 GByte</b>	
	<b>×64</b>	<b>×64</b>	<b>×64</b>	
	<b>1 Rank (×16)</b>	<b>2 Ranks (×16)</b>	<b>2 Ranks (×8)</b>	
Label Code		PC2-3200S-333	PC2-3200S-333	PC2-3200S-333
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
0	Programmed SPD Bytes in EEPROM	80	80	80
1	Total number of Bytes in EEPROM	08	08	08
2	Memory Type (DDR2)	08	08	08
3	Number of Row Addresses	0D	0D	0E
4	Number of Column Addresses	0A	0A	0A
5	DIMM Rank and Stacking Information	60	61	61
6	Data Width	40	40	40
7	Not used	00	00	00
8	Interface Voltage Level	05	05	05
9	$t_{CK}$ @ CL <sub>MAX</sub> (Byte 18) [ns]	50	50	50
10	$t_{AC}$ SDRAM @ CL <sub>MAX</sub> (Byte 18) [ns]	60	60	60
11	Error Correction Support (non-ECC, ECC)	00	00	00
12	Refresh Rate and Type	82	82	82
13	Primary SDRAM Width	10	10	08
14	Error Checking SDRAM Width	00	00	00
15	Not used	00	00	00
16	Burst Length Supported	0C	0C	0C
17	Number of Banks on SDRAM Device	04	04	04
18	Supported CAS Latencies	38	38	38
19	DIMM Mechanical Characteristics	01	01	01
20	DIMM Type Information	04	04	04
21	DIMM Attributes	00	00	00
22	Component Attributes	07	07	07
23	$t_{CK}$ @ CL <sub>MAX</sub> -1 (Byte 18) [ns]	50	50	50

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-5-B	HYS64T64020HDL-5-B	HYS64T128021HDL-5-B
Organization	<b>256MB</b>	<b>512MB</b>	<b>1 GByte</b>	
	<b>×64</b>	<b>×64</b>	<b>×64</b>	
	<b>1 Rank (×16)</b>	<b>2 Ranks (×16)</b>	<b>2 Ranks (×8)</b>	
Label Code		PC2-3200S-333	PC2-3200S-333	PC2-3200S-333
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
24	$t_{AC}$ SDRAM @ $CL_{MAX}$ -1 [ns]	60	60	60
25	$t_{CK}$ @ $CL_{MAX}$ -2 (Byte 18) [ns]	50	50	50
26	$t_{AC}$ SDRAM @ $CL_{MAX}$ -2 [ns]	60	60	60
27	$t_{RP,MIN}$ [ns]	3C	3C	3C
28	$t_{RRD,MIN}$ [ns]	28	28	1E
29	$t_{RCD,MIN}$ [ns]	3C	3C	3C
30	$t_{RAS,MIN}$ [ns]	28	28	28
31	Module Density per Rank	40	40	80
32	$t_{AS,MIN}$ and $t_{CS,MIN}$ [ns]	35	35	35
33	$t_{AH,MIN}$ and $t_{CH,MIN}$ [ns]	47	47	47
34	$t_{DS,MIN}$ [ns]	15	15	15
35	$t_{DH,MIN}$ [ns]	27	27	27
36	$t_{WR,MIN}$ [ns]	3C	3C	3C
37	$t_{WTR,MIN}$ [ns]	28	28	28
38	$t_{RTP,MIN}$ [ns]	1E	1E	1E
39	Analysis Characteristics	00	00	00
40	$t_{RC}$ and $t_{RFC}$ Extension	00	00	00
41	$t_{RC,MIN}$ [ns]	37	37	37
42	$t_{RFC,MIN}$ [ns]	69	69	69
43	$t_{CK,MAX}$ [ns]	80	80	80
44	$t_{DQSQ,MAX}$ [ns]	23	23	23
45	$t_{QHS,MAX}$ [ns]	2D	2D	2D
46	PLL Relock Time	00	00	00
47	$T_{CASE,MAX}$ Delta / $\Delta T_{4R4W}$ Delta	54	54	50
48	Psi(T-A) DRAM	72	72	7A
49	$\Delta T_0$ (DT0)	4B	4B	3B

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Product Type		HYS64T32000HDL-5-B	HYS64T64020HDL-5-B	HYS64T128021HDL-5-B
Organization	256MB	512MB	1 GByte	
	×64	×64	×64	
	1 Rank (×16)	2 Ranks (×16)	2 Ranks (×8)	
Label Code		PC2-3200S-333	PC2-3200S-333	PC2-3200S-333
JEDEC SPD Revision		Rev. 1.2	Rev. 1.2	Rev. 1.2
Byte#	Description	HEX	HEX	HEX
50	$\Delta T_{2N}$ (DT2N, UDIMM) or $\Delta T_{2Q}$ (DT2Q, RDIMM)	25	25	27
51	$\Delta T_{2P}$ (DT2P)	33	33	36
52	$\Delta T_{3N}$ (DT3N)	1C	1C	1E
53	$\Delta T_{3P,\text{fast}}$ (DT3P fast)	34	34	38
54	$\Delta T_{3P,\text{slow}}$ (DT3P slow)	27	27	2A
55	$\Delta T_{4R}$ (DT4R) / $\Delta T_{4R4W}$ Sign (DT4R4W)	3E	3E	38
56	$\Delta T_{5B}$ (DT5B)	1B	1B	1D
57	$\Delta T_7$ (DT7)	30	30	21
58	Psi(ca) PLL	00	00	00
59	Psi(ca) REG	00	00	00
60	$\Delta T_{\text{PLL}}$ (DTPLL)	00	00	00
61	$\Delta T_{\text{REG}}$ (DTREG) / Toggle Rate	00	00	00
62	SPD Revision	12	12	12
63	Checksum of Bytes 0-62	6F	70	8E
64	Manufacturer's JEDEC ID Code (1)	7F	7F	7F
65	Manufacturer's JEDEC ID Code (2)	7F	7F	7F
66	Manufacturer's JEDEC ID Code (3)	7F	7F	7F
67	Manufacturer's JEDEC ID Code (4)	7F	7F	7F
68	Manufacturer's JEDEC ID Code (5)	7F	7F	7F
69	Manufacturer's JEDEC ID Code (6)	51	51	51
70	Manufacturer's JEDEC ID Code (7)	00	00	00
71	Manufacturer's JEDEC ID Code (8)	00	00	00
72	Module Manufacturer Location	xx	xx	xx
73	Product Type, Char 1	36	36	36
74	Product Type, Char 2	34	34	34
75	Product Type, Char 3	54	54	54

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

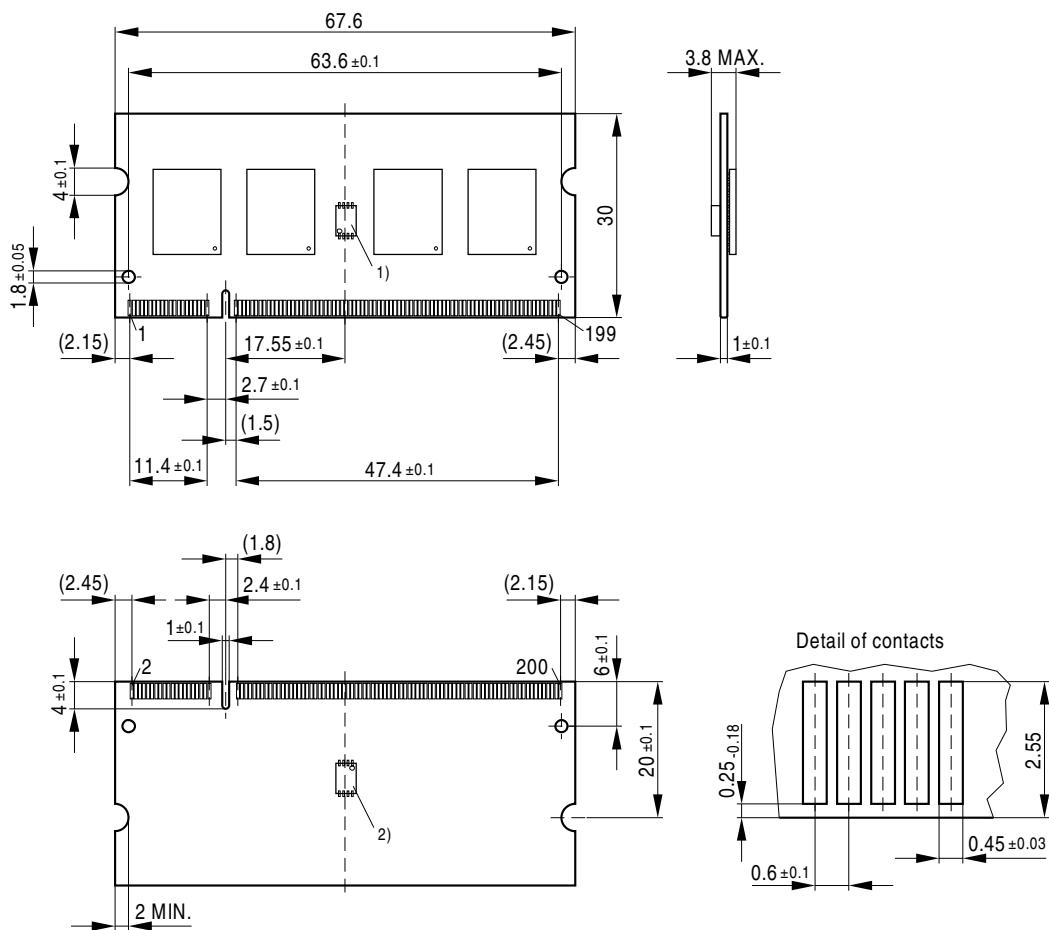
<b>Product Type</b>		HYS64T32000HDL-5-B	HYS64T64020HDL-5-B	HYS64T128021HDL-5-B
<b>Organization</b>	<b>256MB</b>	<b>512MB</b>	<b>1 GByte</b>	
	<b>×64</b>	<b>×64</b>	<b>×64</b>	
	<b>1 Rank (×16)</b>	<b>2 Ranks (×16)</b>	<b>2 Ranks (×8)</b>	
<b>Label Code</b>		PC2-3200S-333	PC2-3200S-333	PC2-3200S-333
<b>JEDEC SPD Revision</b>		<b>Rev. 1.2</b>	<b>Rev. 1.2</b>	<b>Rev. 1.2</b>
<b>Byte#</b>	<b>Description</b>	<b>HEX</b>	<b>HEX</b>	<b>HEX</b>
76	Product Type, Char 4	33	36	31
77	Product Type, Char 5	32	34	32
78	Product Type, Char 6	30	30	38
79	Product Type, Char 7	30	32	30
80	Product Type, Char 8	30	30	32
81	Product Type, Char 9	48	48	31
82	Product Type, Char 10	44	44	48
83	Product Type, Char 11	4C	4C	44
84	Product Type, Char 12	35	35	4C
85	Product Type, Char 13	42	42	35
86	Product Type, Char 14	20	20	42
87	Product Type, Char 15	20	20	20
88	Product Type, Char 16	20	20	20
89	Product Type, Char 17	20	20	20
90	Product Type, Char 18	20	20	20
91	Module Revision Code	4x	4x	4x
92	Test Program Revision Code	xx	xx	xx
93	Module Manufacturing Date Year	xx	xx	xx
94	Module Manufacturing Date Week	xx	xx	xx
95 - 98	Module Serial Number	xx	xx	xx
99 - 127	Not used	00	00	00
128 - 255	Blank for customer use	FF	FF	FF



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

## 5 Package Outlines

**FIGURE 5**  
Package Outline Raw Card C L-DIM-200-30



- Drawing according to ISO 8015
- General tolerances  $\pm 0.15$
- Dimensions in mm

FPO\_L\_-DIM\_\_\_\_-200-030

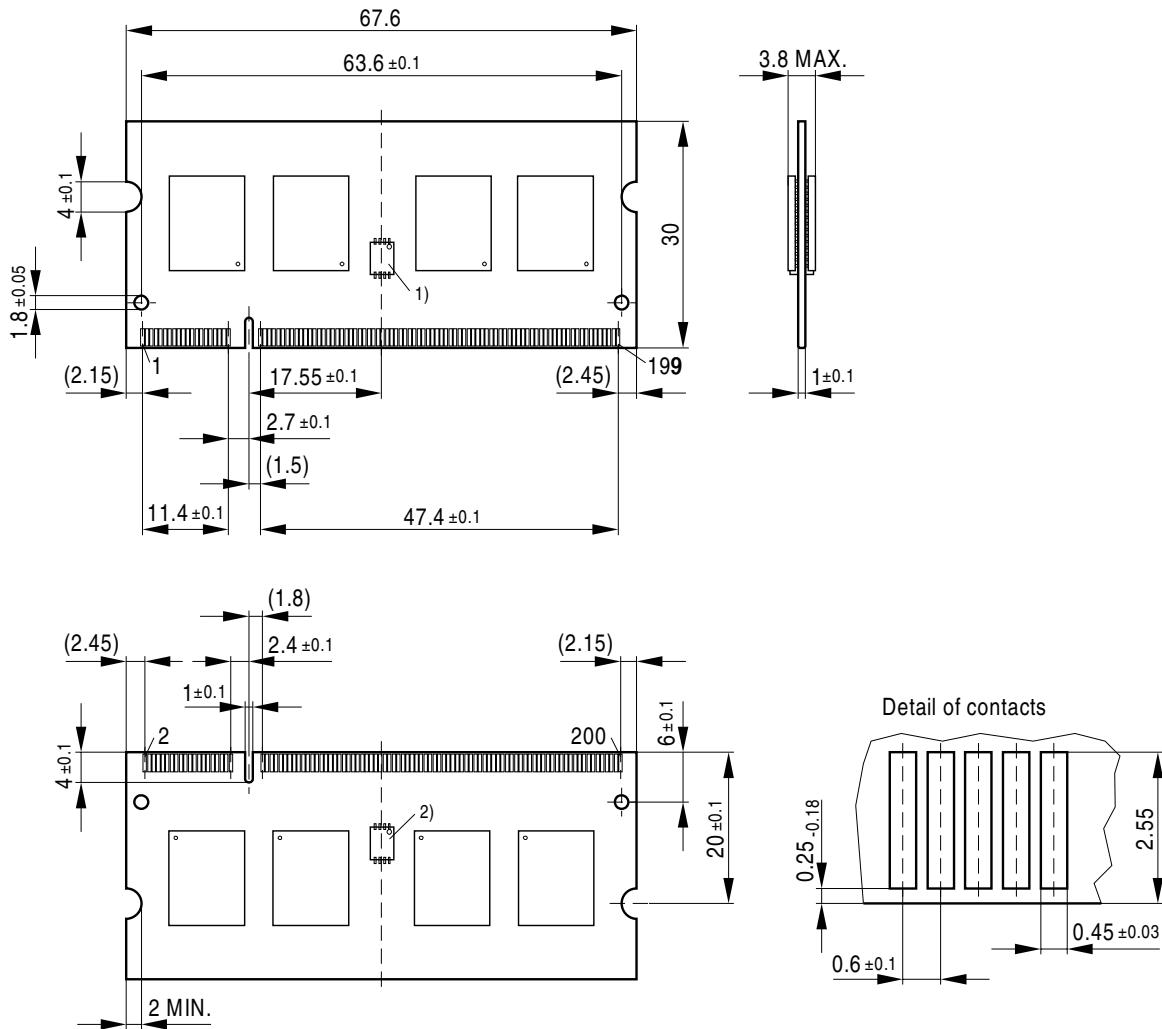
### Notes

1. Thermal Sensor (Optional)
2. SPD or Combidevice (if used then no Thermal Sensor needed)



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

**FIGURE 6**  
Package Outline Raw Card A L-DIM-200-31



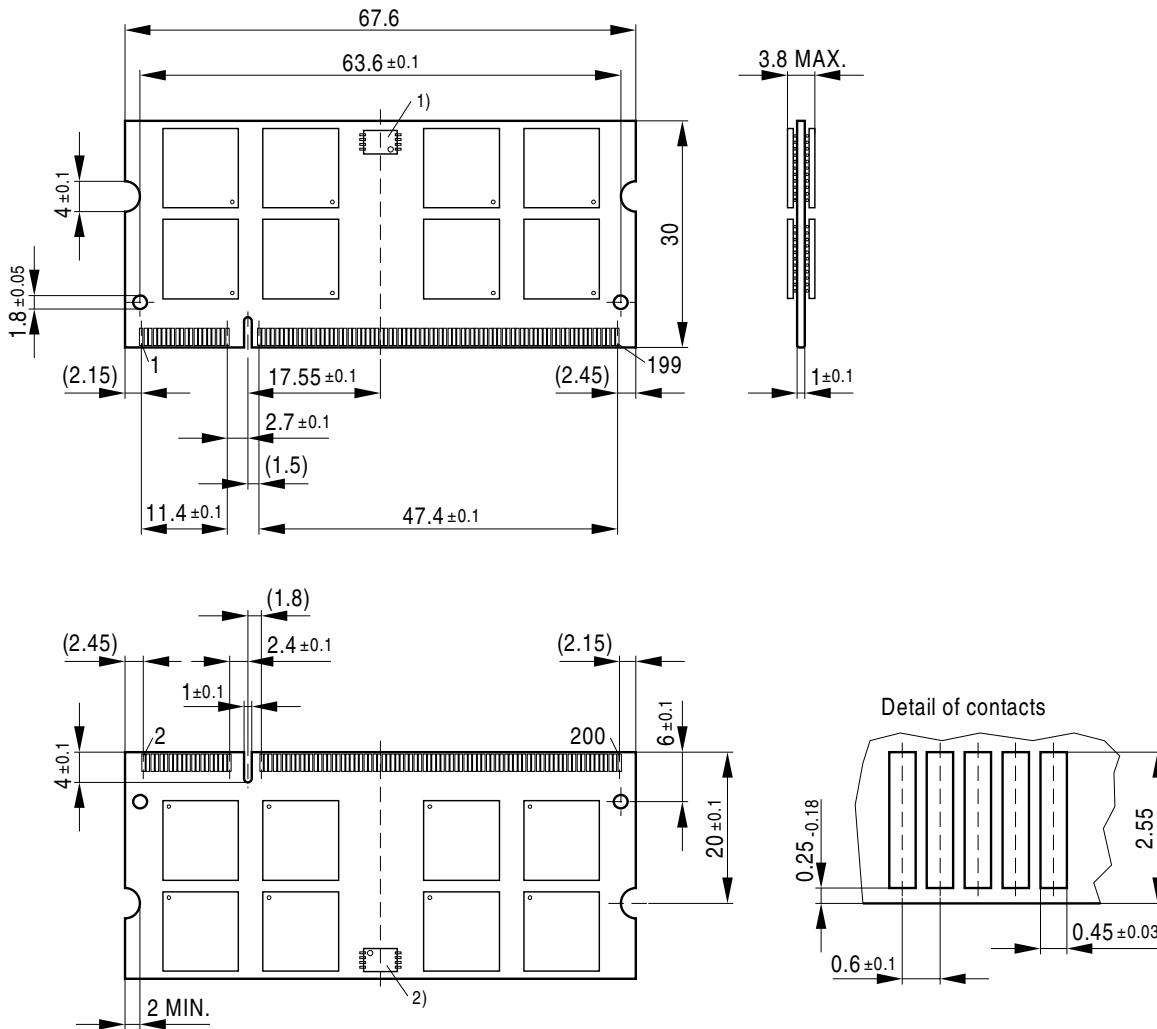
#### Notes

1. Thermal Sensor (Optional)
2. SPD or Combidevice (if used then no Thermal Sensor needed)



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

**FIGURE 7**  
Package Outline Raw Card E L-DIM-200-36



#### Notes

1. SPD or Combidevice (if used then no Thermal Sensor needed)
2. Thermal Sensor (Optional)

HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

## 6 Product Type Nomenclature

Qimonda's nomenclature uses simple coding combined with some proprietary coding. **Table 31** provides examples for module and component product type number as well as the

field number. The detailed field description together with possible values and coding explanation is listed for modules in **Table 32** and for components in **Table 33**.

**TABLE 31**  
**Nomenclature Fields and Examples**

Example for	Field Number										
	1	2	3	4	5	6	7	8	9	10	11
Micro-DIMM	HYS	64	T	64/128	0	2	0	K	M	-5	-A
DDR2 DRAM	HYB	18	T	512/1G	16		0	A	C	-5	

**TABLE 32**  
**DDR2 DIMM Nomenclature**

Field	Description	Values	Coding
1	Qimonda Module Prefix	HYS	Constant
2	Module Data Width [bit]	64	Non-ECC
		72	ECC
3	DRAM Technology	T	DDR2
4	Memory Density per I/O [Mbit]; Module Density <sup>1)</sup>	32	256 MByte
		64	512 MByte
		128	1 GByte
		256	2 GByte
		512	4 GByte
5	Raw Card Generation	0 .. 9	Look up table
6	Number of Module Ranks	0, 2, 4	1, 2, 4
7	Product Variations	0 .. 9	Look up table
8	Package, Lead-Free Status	A .. Z	Look up table
9	Module Type	D	SO-DIMM
		M	Micro-DIMM
		R	Registered
		U	Unbuffered
		F	Fully Buffered



HYS64T[32/64/128]xxxHDL-[25F/2.5/3/3S/3.7/5]-B  
SO-DIMM DDR2 SDRAM Module

Field	Description	Values	Coding
10	Speed Grade	-19F	PC2-8500 6-6-6
		-1.9	PC2-8500 7-7-7
		-25F	PC2-6400 5-5-5
		-2.5	PC2-6400 6-6-6
		-3	PC2-5300 4-4-4
		-3S	PC2-5300 5-5-5
		-3.7	PC2-4200 4-4-4
		-5	PC2-3200 3-3-3
11	Die Revision	-A	First
		-B	Second

- 1) Multiplying "Memory Density per I/O" with "Module Data Width" and dividing by 8 for Non-ECC and 9 for ECC modules gives the overall module memory density in MBytes as listed in column "Coding".

**TABLE 33**  
**DDR2 DRAM Nomenclature**

Field	Description	Values	Coding
1	Qimonda Component Prefix	HYB	Constant
2	Interface Voltage [V]	18	SSTL_18
3	DRAM Technology	T	DDR2
4	Component Density [Mbit]	256	256 Mbit
		512	512 Mbit
		1G	1 Gbit
		2G	2 Gbit
5+6	Number of I/Os	40	x4
		80	x8
		16	x16
7	Product Variations	0 .. 9	Look up table
8	Die Revision	A	First
		B	Second
9	Package, Lead-Free Status	C	FBGA, lead-containing
		F	FBGA, lead-free
10	Speed Grade	-19F	PC2-8500 6-6-6
		-1.9	PC2-8500 7-7-7
		-25F	PC2-6400 5-5-5
		-2.5	PC2-6400 6-6-6
		-3	PC2-5300 4-4-4
		-3S	PC2-5300 5-5-5
		-3.7	PC2-4200 4-4-4
		-5	PC2-3200 3-3-3



# Contents

<b>1</b>	<b>Overview</b>	3
1.1	Features	3
1.2	Description	4
<b>2</b>	<b>Pin Configurations</b>	6
2.1	Pin Configurations	6
<b>3</b>	<b>Electrical Characteristics</b>	13
3.1	Absolute Maximum Ratings	13
3.2	DC Operating Conditions	14
3.3	Timing Characteristics	15
3.3.1	Speed Grade Definitions	15
3.3.2	Component AC Timing Parameters	16
3.3.3	ODT AC Electrical Characteristics	24
3.4	I <sub>DD</sub> Specifications and Conditions	25
<b>4</b>	<b>SPD Codes</b>	30
<b>5</b>	<b>Package Outlines</b>	63
<b>6</b>	<b>Product Type Nomenclature</b>	66

**Edition 2007-10**

**Published by Qimonda AG**  
**Gustav-Heinemann-Ring 212**  
**D-81739 München, Germany**  
© Qimonda AG 2007.  
All Rights Reserved.

**Legal Disclaimer**

The information given in this Internet Data Sheet shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie"). With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Qimonda hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

**Information**

For further information on technology, delivery terms and conditions and prices please contact your nearest Qimonda Office.

**Warnings**

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Qimonda Office.

Qimonda Components may only be used in life-support devices or systems with the express written approval of Qimonda, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.